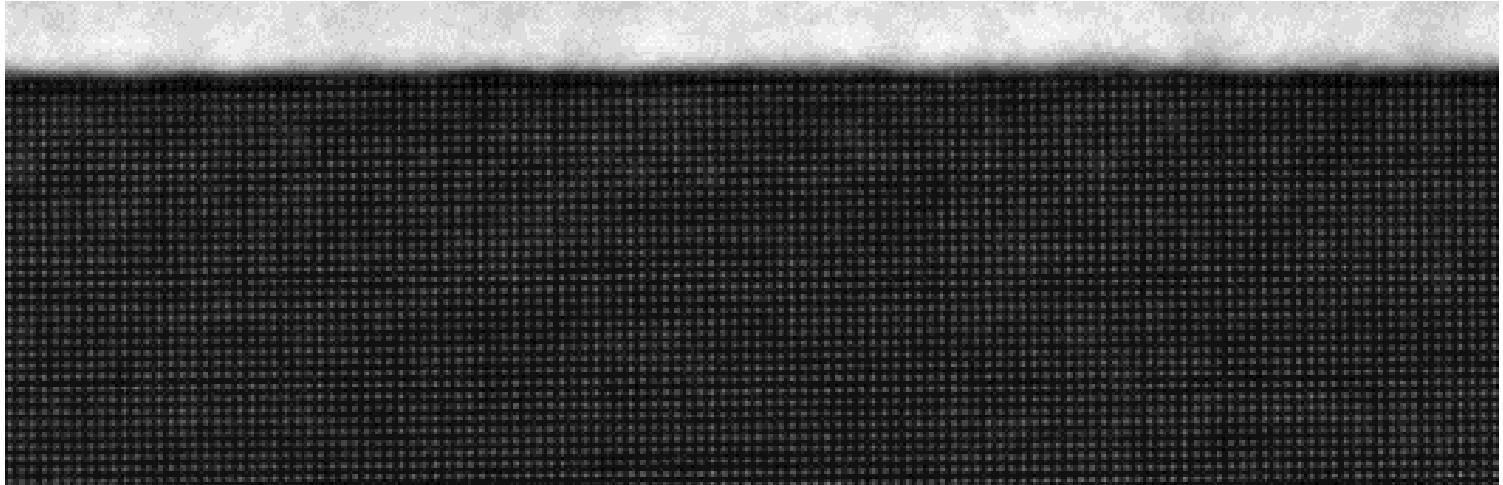


Física del Estado Sólido

Sólidos con simetría de traslación



FABRICACION DE MATERIALES/ MUESTRAS

Métodos químicos y físicos

nano (top-down) desde la fisica

Alto vacio

Ultra alto vacio

Micro y nanofabricacion

CARACTERIZACION

Enfoque : local / medio

Facilidades multiusuarios luz sinchrotron

neutrones

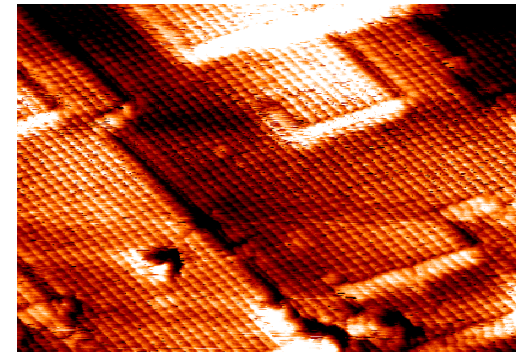
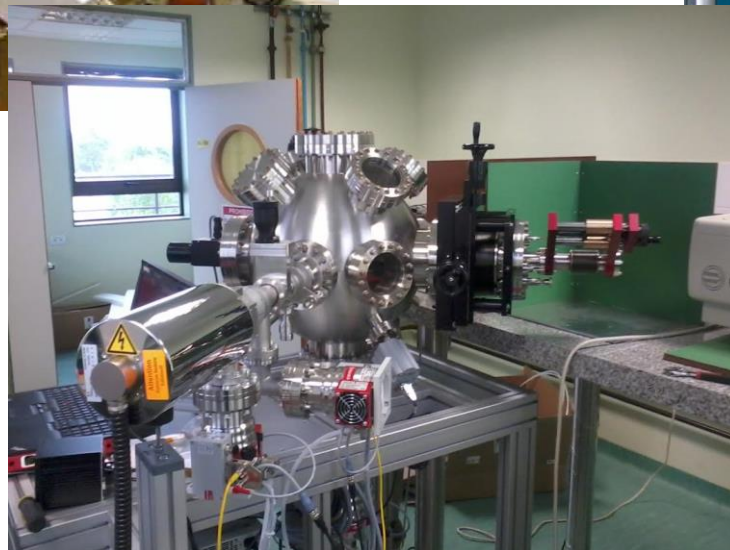
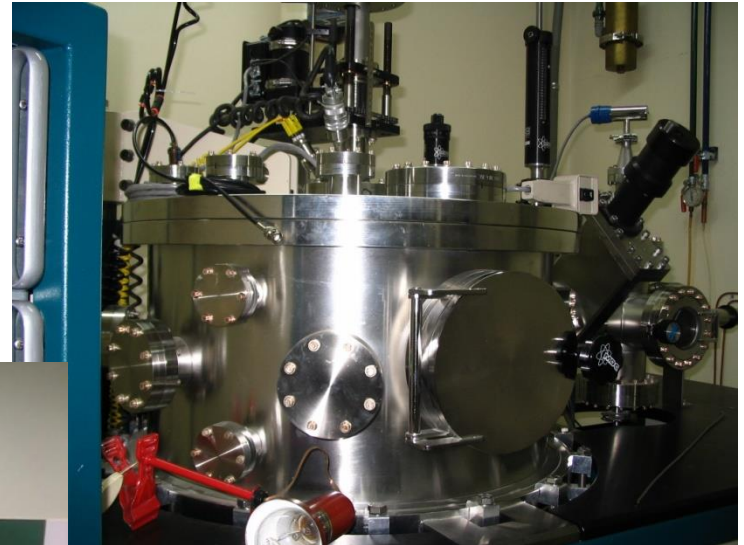
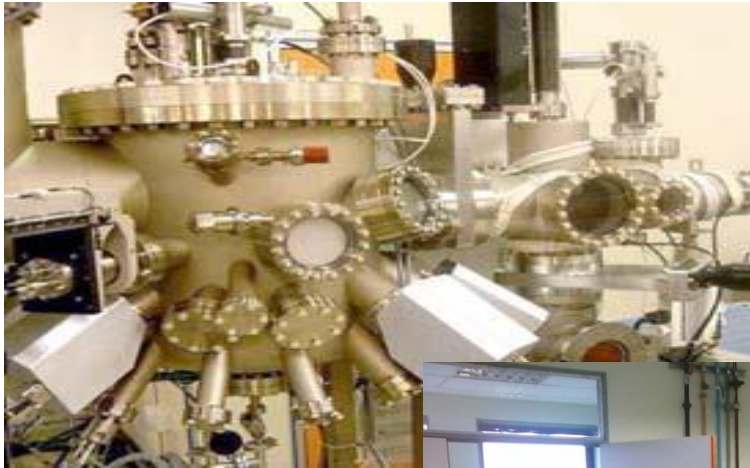
Metodos quimicos: polvos, ceramicos, particulas, alambres y tubos

Metodos fisicos: peliculas delgadas y multicapas

HV Ablasion Laser (2-10nm/min)

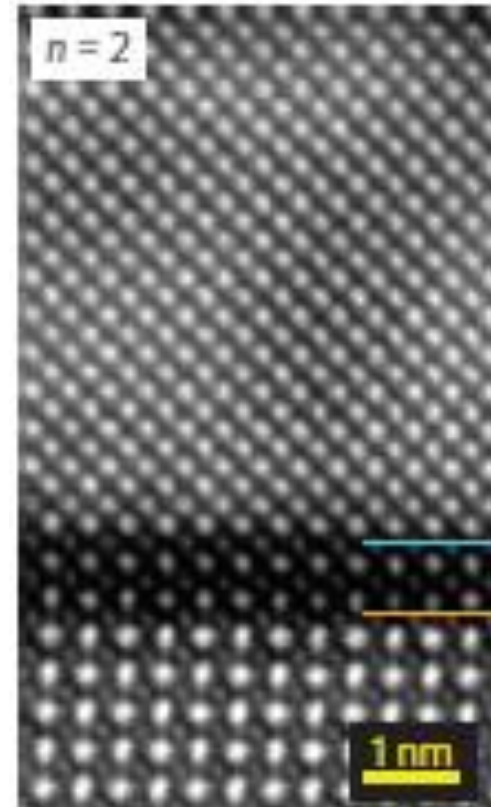
Sputtering (1-10nm/min)

UHV Molecular Beam Epitaxy (MBE) (0.05 – 1nm/min)



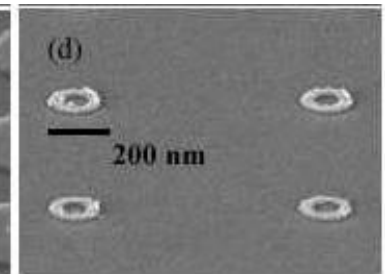
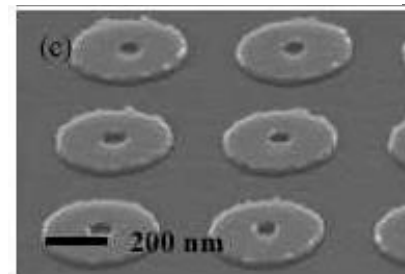
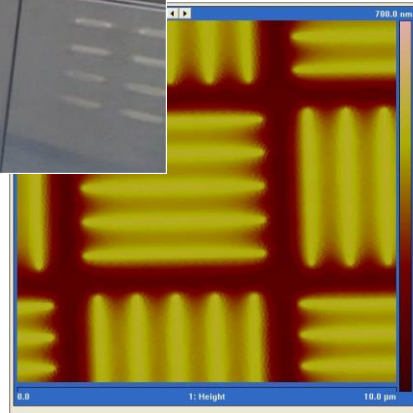
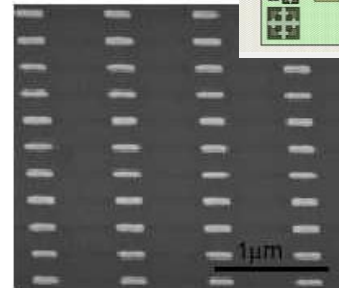
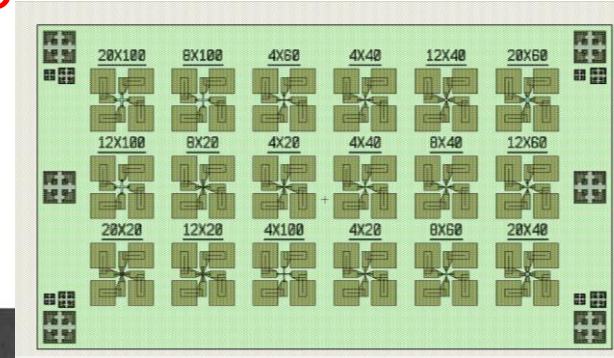
“DISEÑO DE MATERIALES A MEDIDA”

- + Apilando materiales de distintas características
- + Acoplando interfaces terminadas de manera controlada
- + Modificando interfaces con sustratos/ buffers: contenido O, distorsión de red, tensiones....



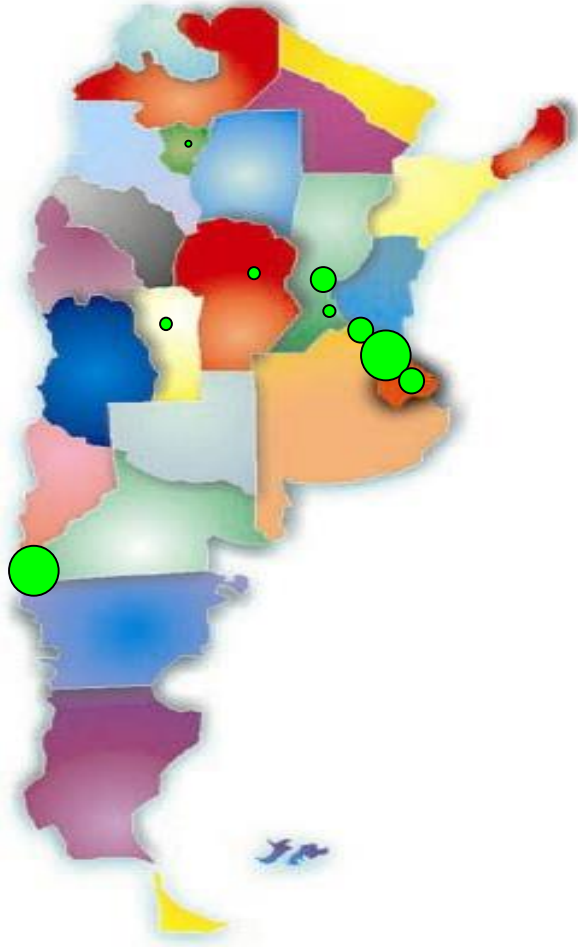
μ y nanoESTRUCTURACION de MUESTRAS Y DISPOSITIVOS

LITOGRAFIA + EROSION
FOCUSED ION BEAM (FIB), ETC



Litografia optica y electronica
Ataques quimicos, ionicos, ionicos reactivos

Facilidades de Nanofabricacion en Argentina



Litografia electronica

Litografia Optica (UV)

Deposito de metales y dielectricos

Comido quimico - fisico

Nanofib

Tratamientos termicos

Microscopia electronica de barrido

Caracterizacion

Montaje Chips : bonding

Grabado de muestras por técnicas litograficas

- 1- Se transfiere un patron definido, a traves de una mascara sobre una resina foto sensible (resol. micron). Caso electrones no hace falta mascara (resol. decenas nm).
- 2- Revela resina y se remueve resina no Iluminada (segun el tipo de resina, podria ser al revés => parte la resina iluminada)
- 3- Erosion ionica o quimica
- 4 Se remueve resto de resina

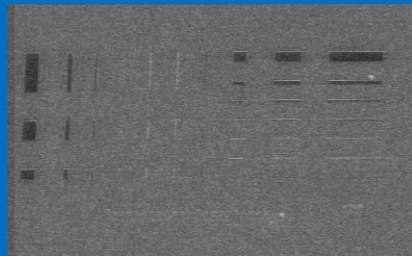
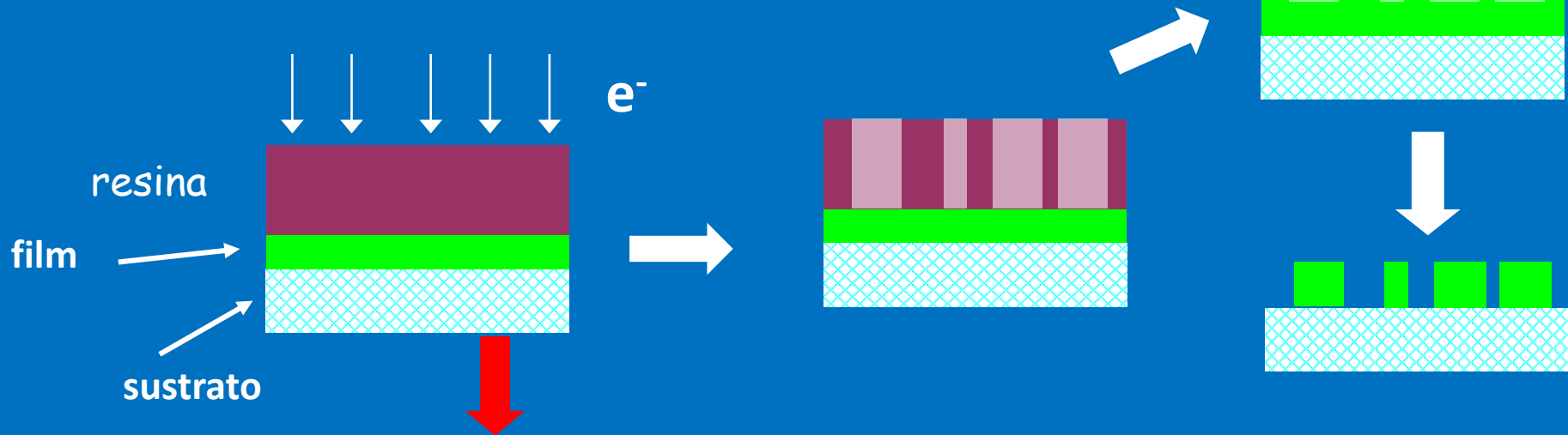
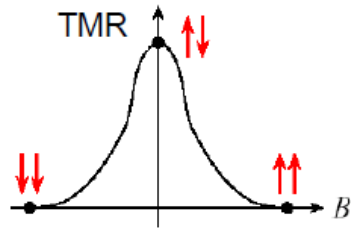
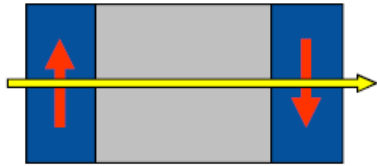
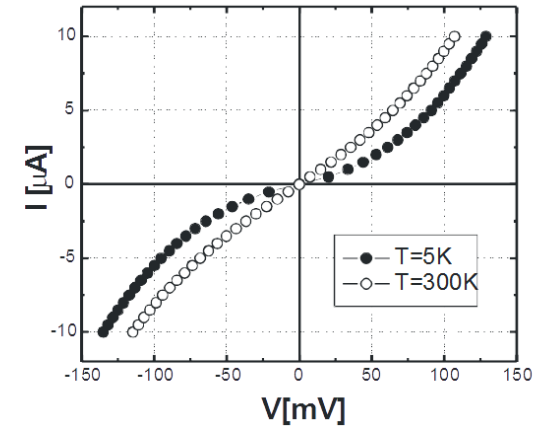


Imagen SEM de la muestra luego de ser litografiada

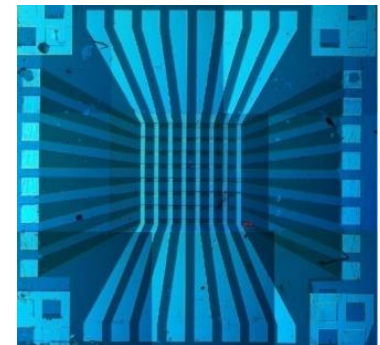
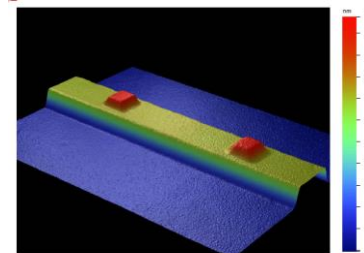
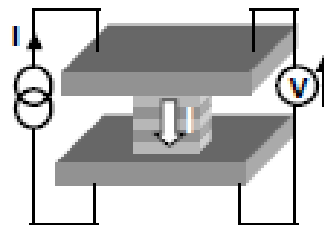
DISPOSITIVOS: EJ. JUNTURAS TÚNEL



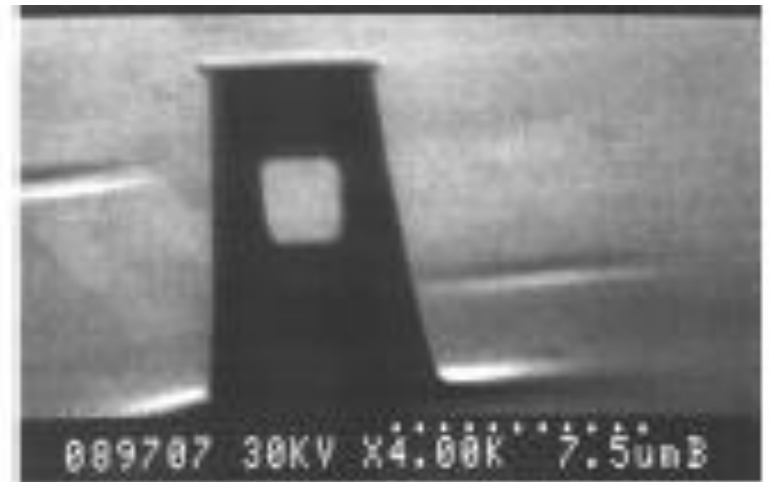
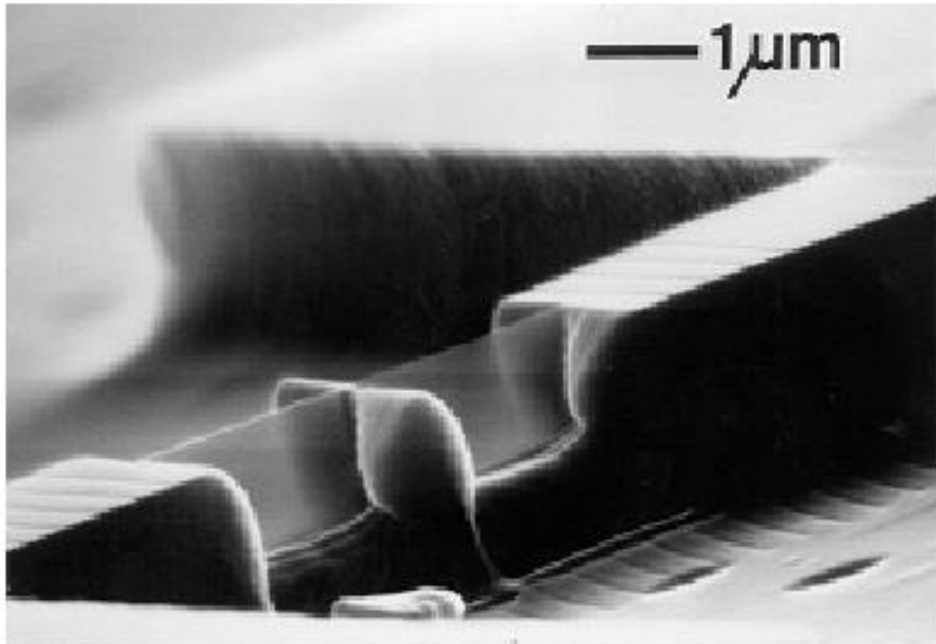
$$\text{TMR} = (g^P - g^{AP}) / (g^P + g^{AP})$$



M. Julliere, Phys. Lett. **54A**, 225 (1975)
 J. S. Moodera et al., Phys. Rev. Lett. **74**, 3273 (1995)



Focused Ion Beam (FIB). Aplicaciones

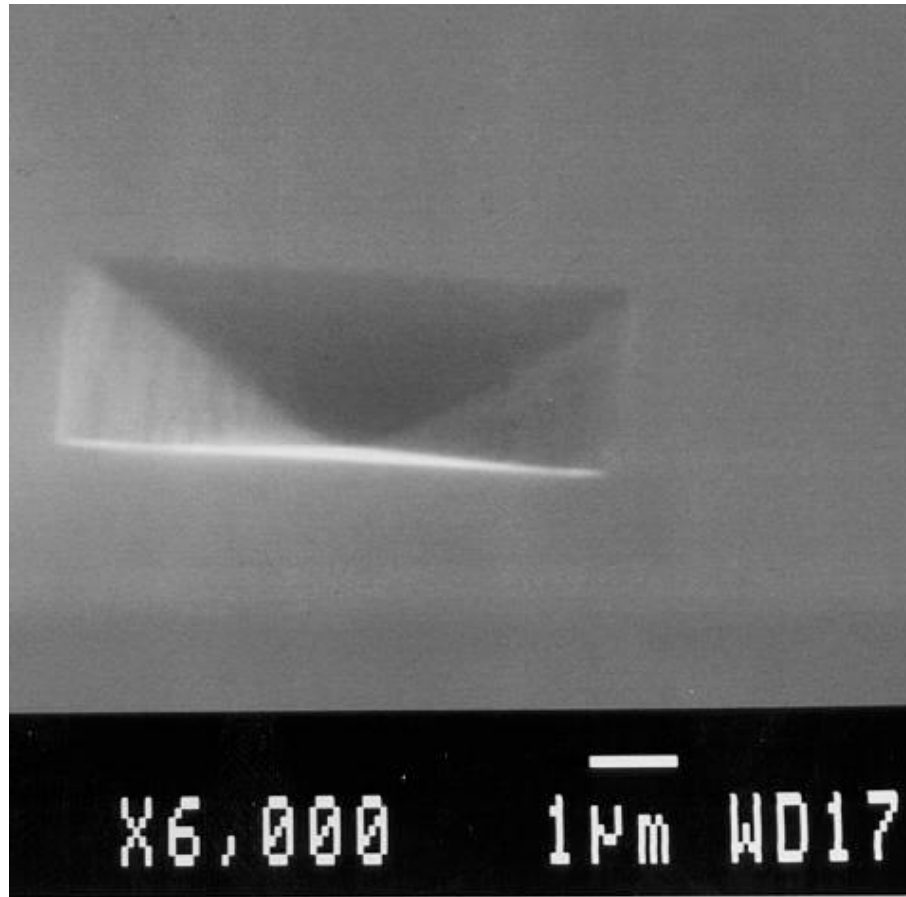


Drilling a hole in a pillar

Specimen preparation for TEM microscopy

(ex L2M): LPN

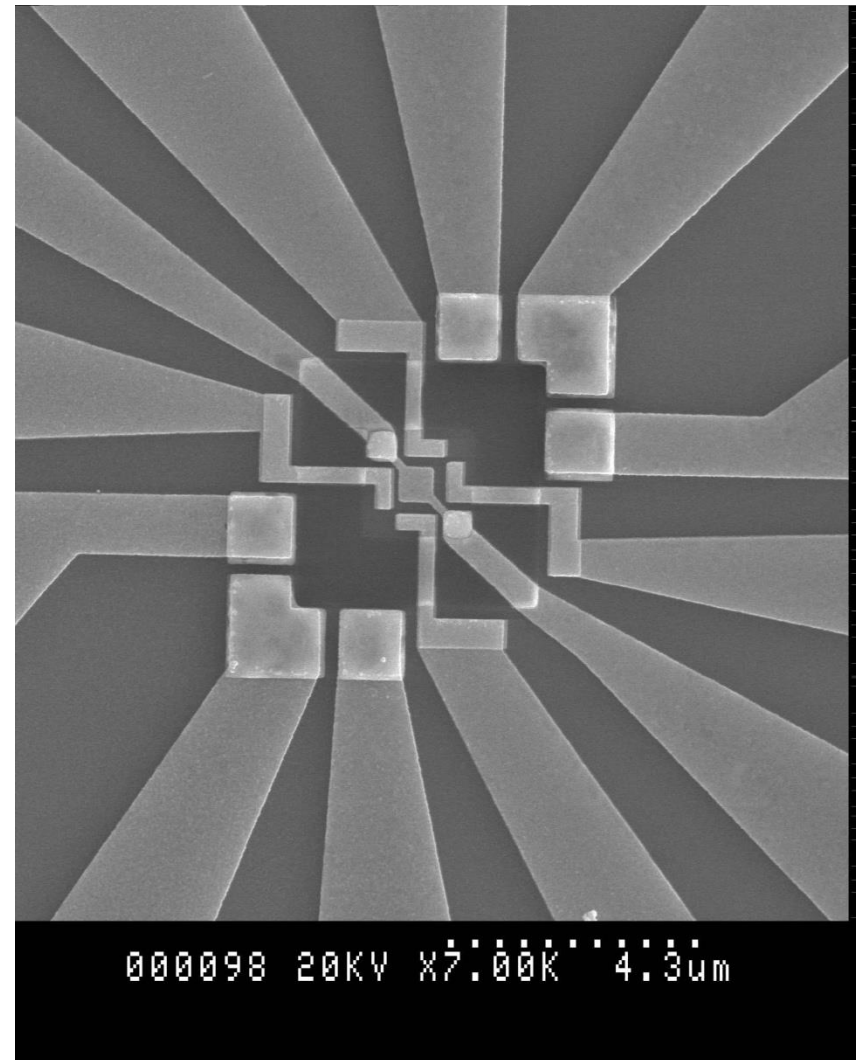
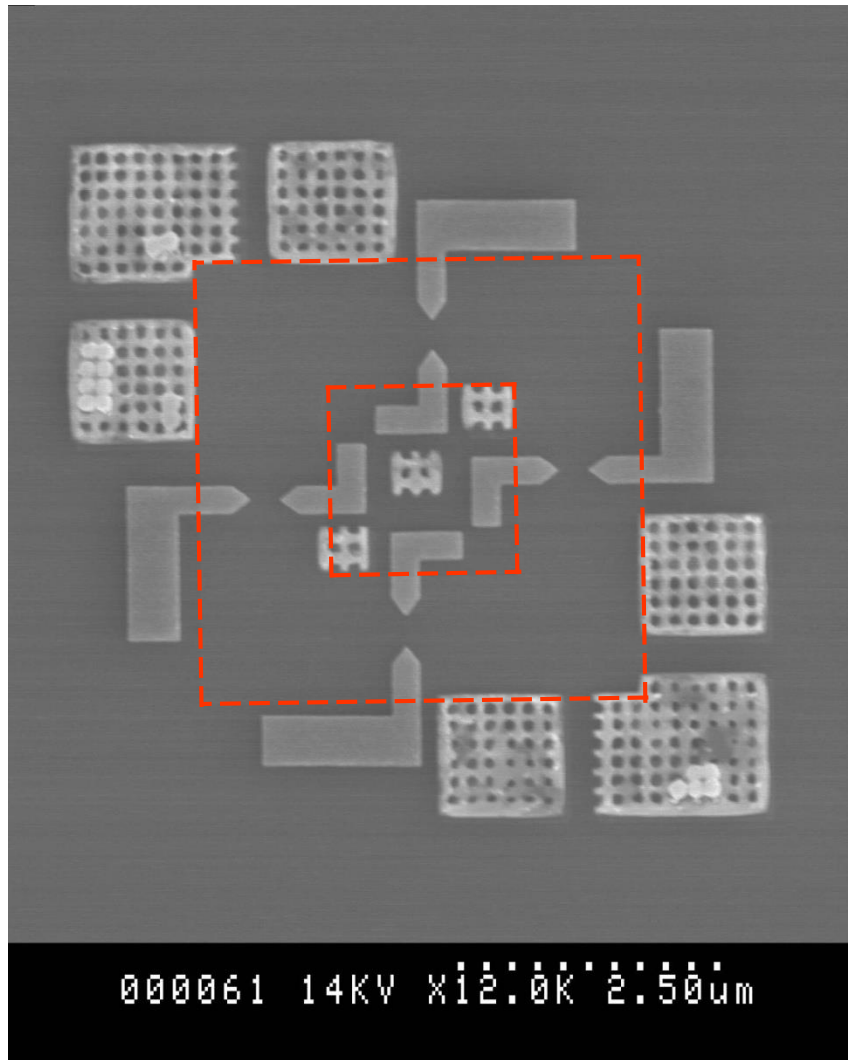
Grabado 3D

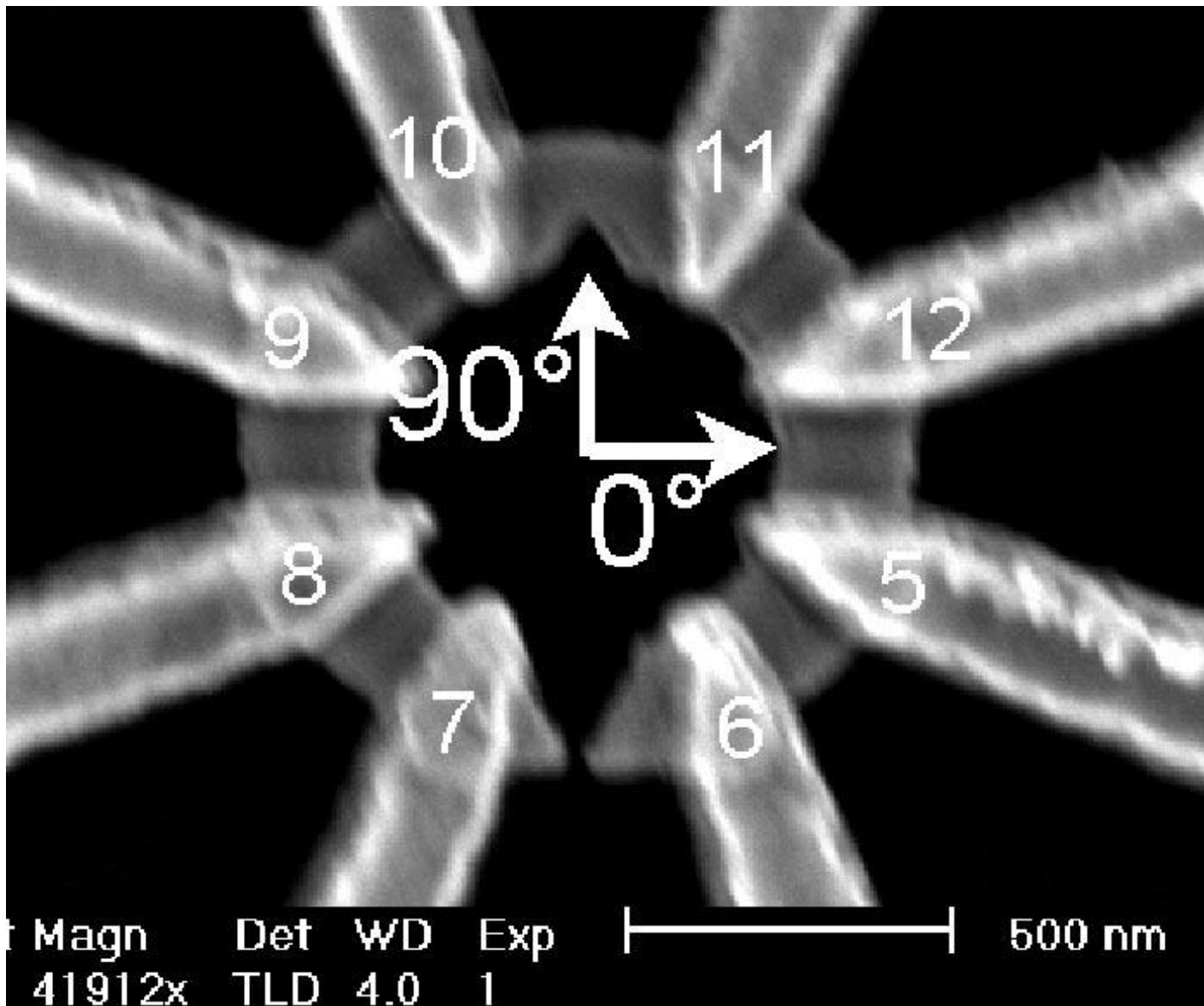


(ex L2M): LPN

Interferometro HBT

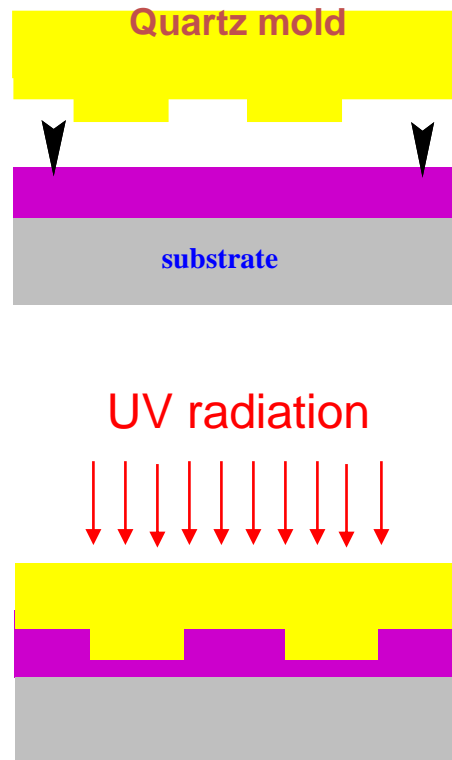
Coherence of a quantum state





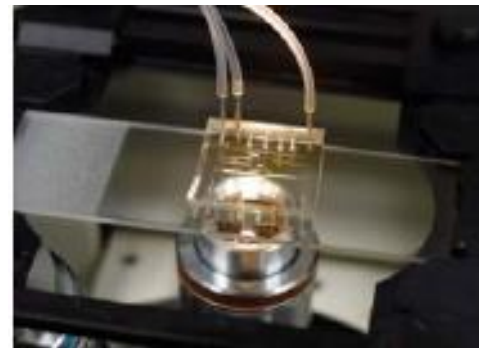
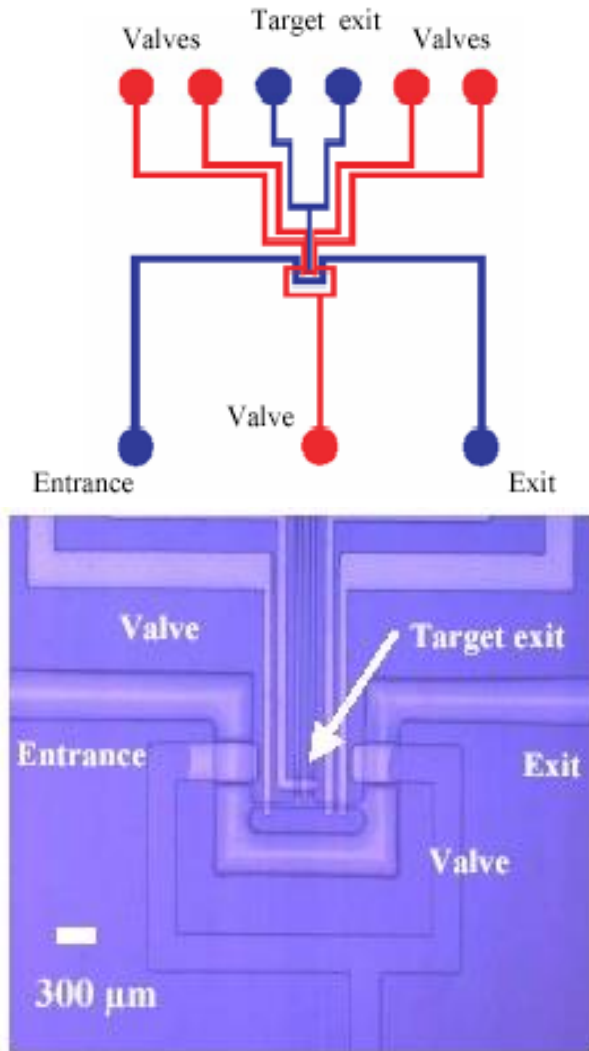
LPN
Konstanz Un.
Cambridge Un.

Mezcla de dos liquidos



UV hardening of the resist

Clasificador de células de mamíferos



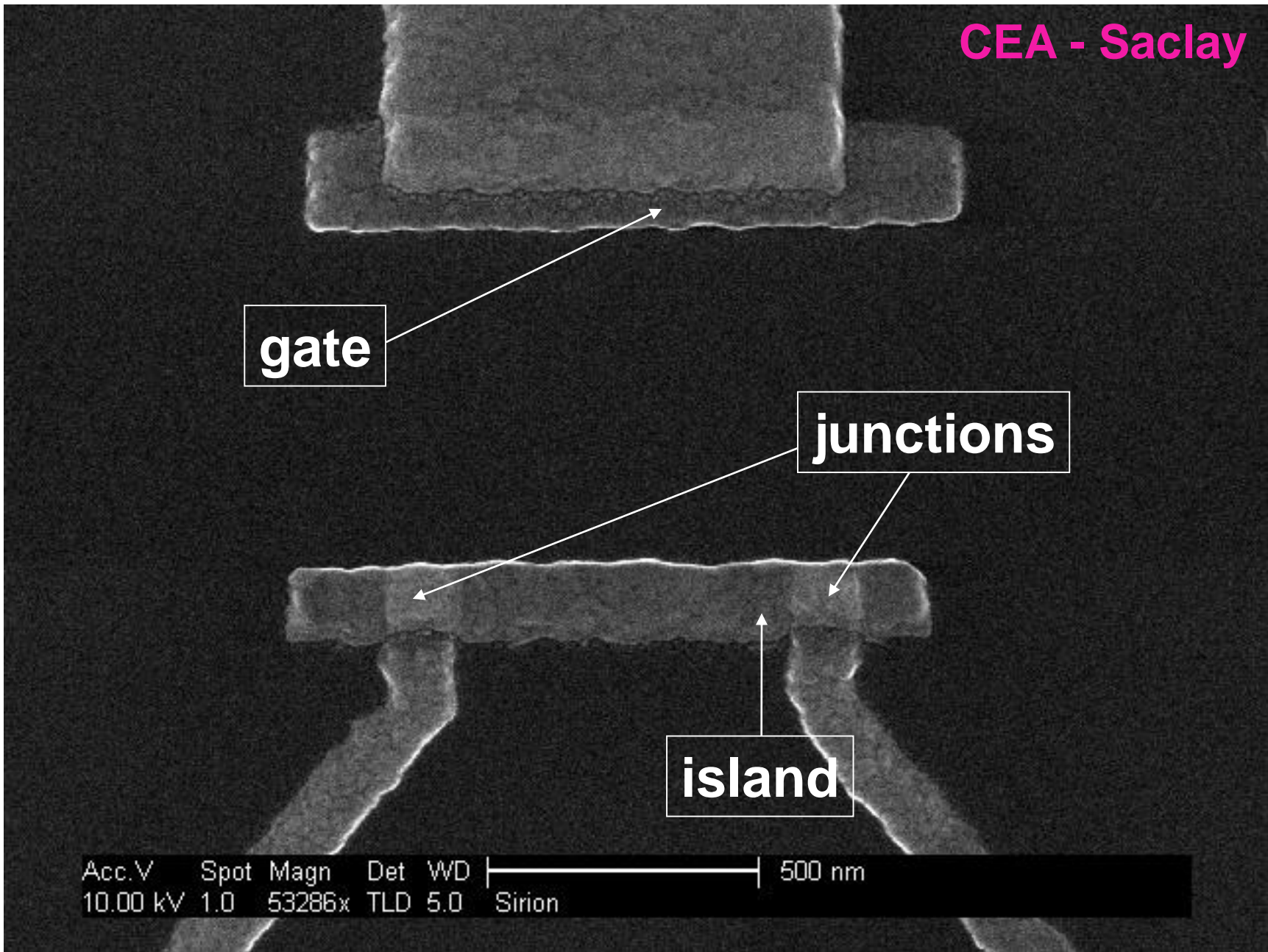
V. Studer , R. Jameson, E. Pellereau, A. Pépin et Y. Chen (MNE 2003)

gate

junctions

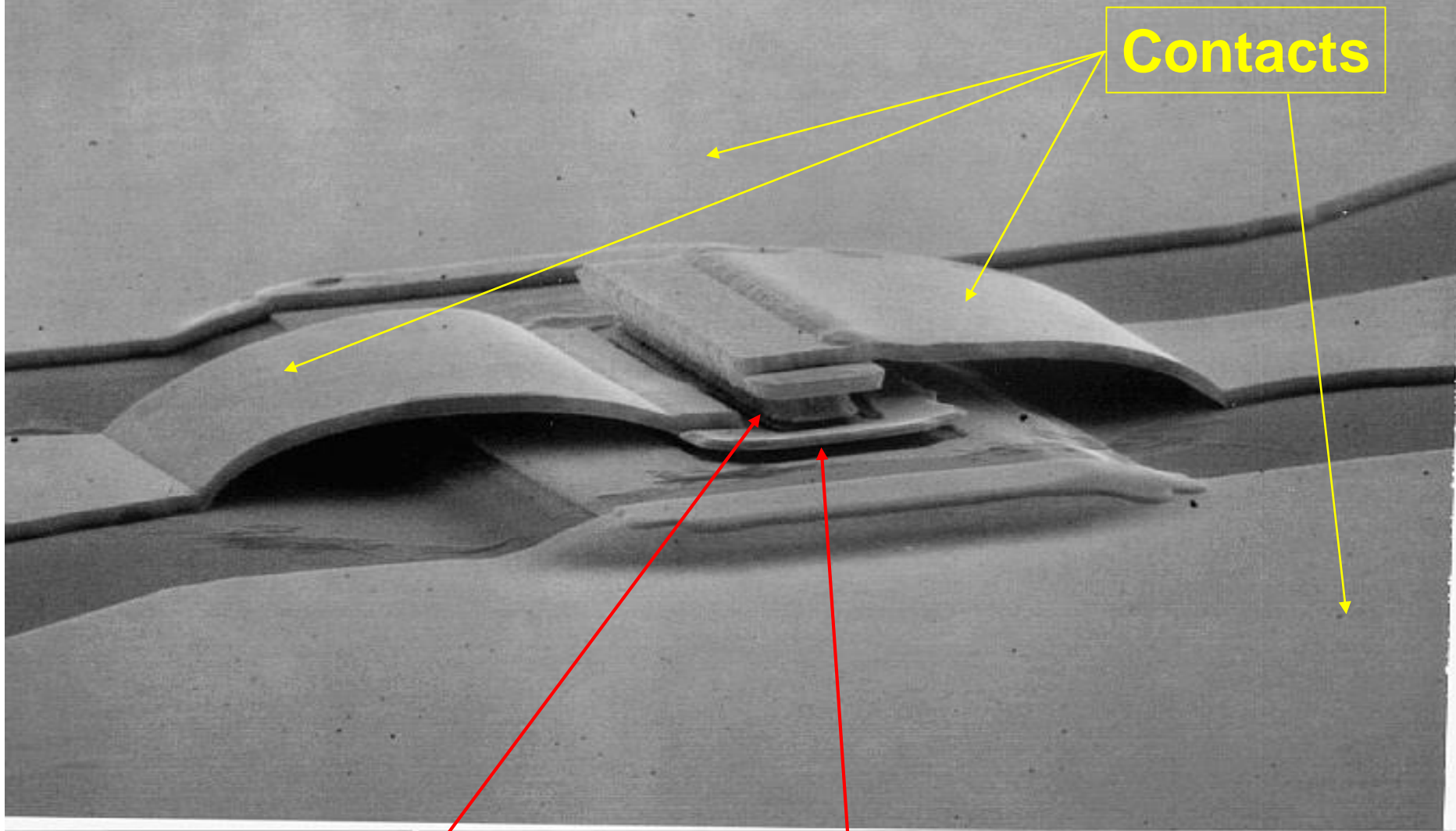
island

Acc.V Spot Magn Det WD |-----| 500 nm
10.00 kV 1.0 53286x TLD 5.0 Sirion



4,15KX 25KV WD:14MM S:00000 P:00000
10UM

Contacts



The chemically controlled over-etch permits to avoid short-cuts between contacts

LPN

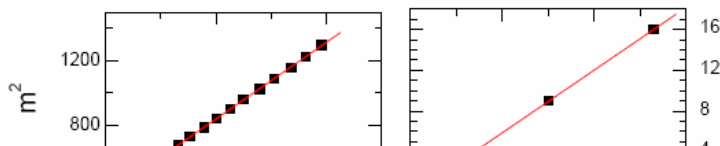
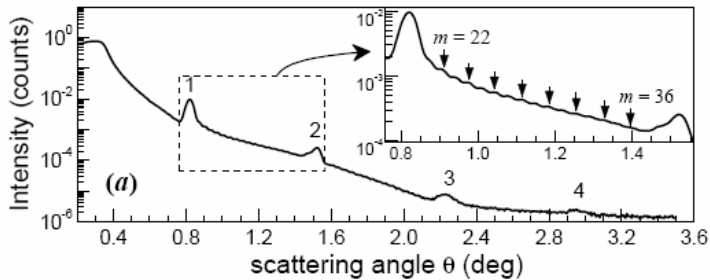
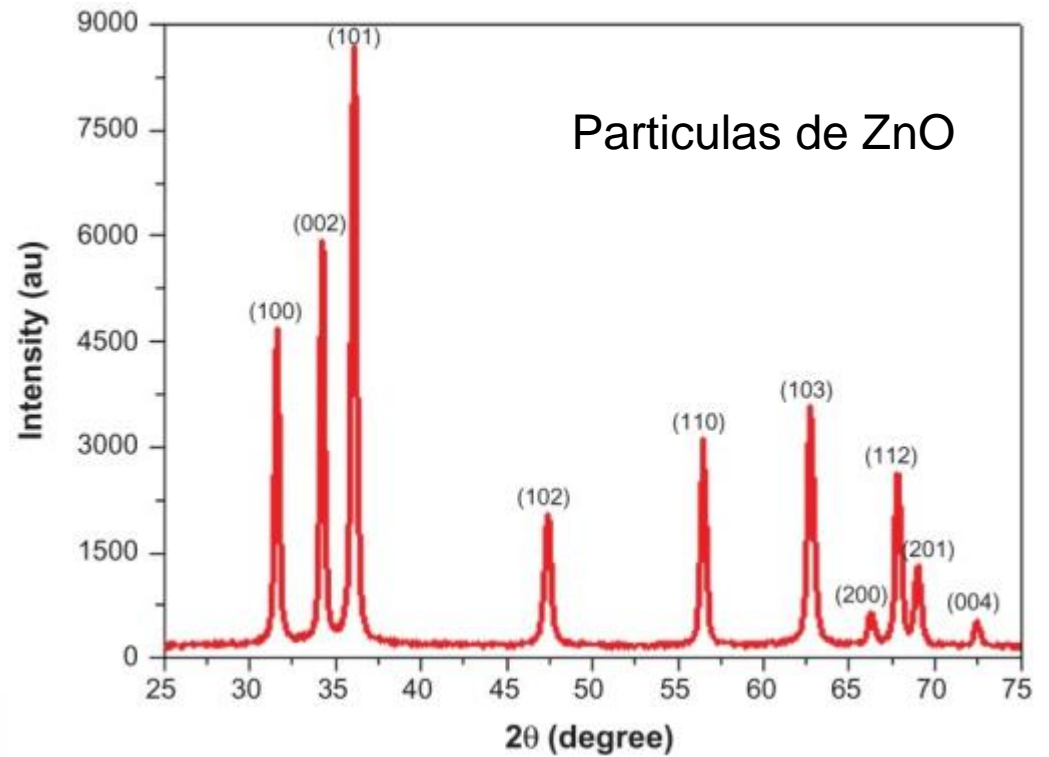
TECNICAS EXPERIMENTALES PARA EL ESTUDIO DE MATERIA CONDENSADA

- Estructura cristalina
- Fonones
- Electrones => espectroscopia de superficies, transporte electrico
- Semiconductores
- Transporte electronico
- Magnetismo

ESTRUCTURA CRISTALINA

Difracción de rayos X

Estructura en polvos,
Textura en films
Parametros de red



Reflectividad de rayos X
($\text{La}_{0.75}\text{Sr}_{0.25}\text{MnO}_3 / \text{LaNiO}_3$)x20



EXAFS Y XANES

Experimento de absorción de rayos X.

Sensibilidad elemental

Permite determinar

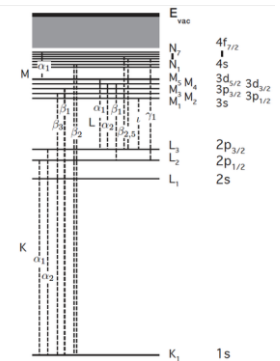
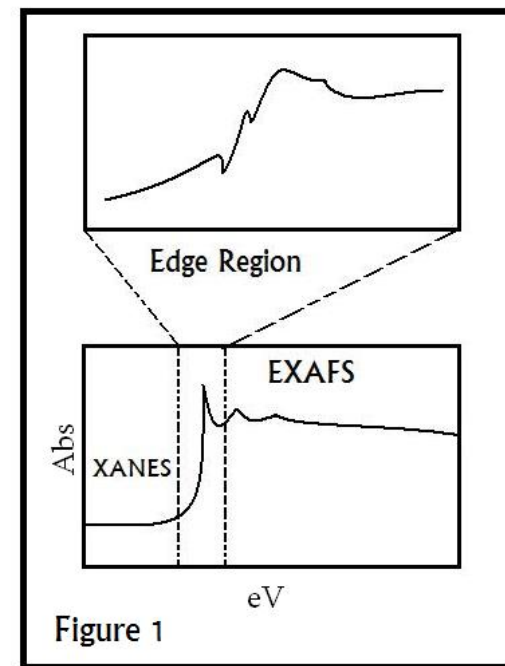
Estado de oxidación

Numero de coordinación

Desorden respecto a los atomos vecinos

Distancia a vecinos

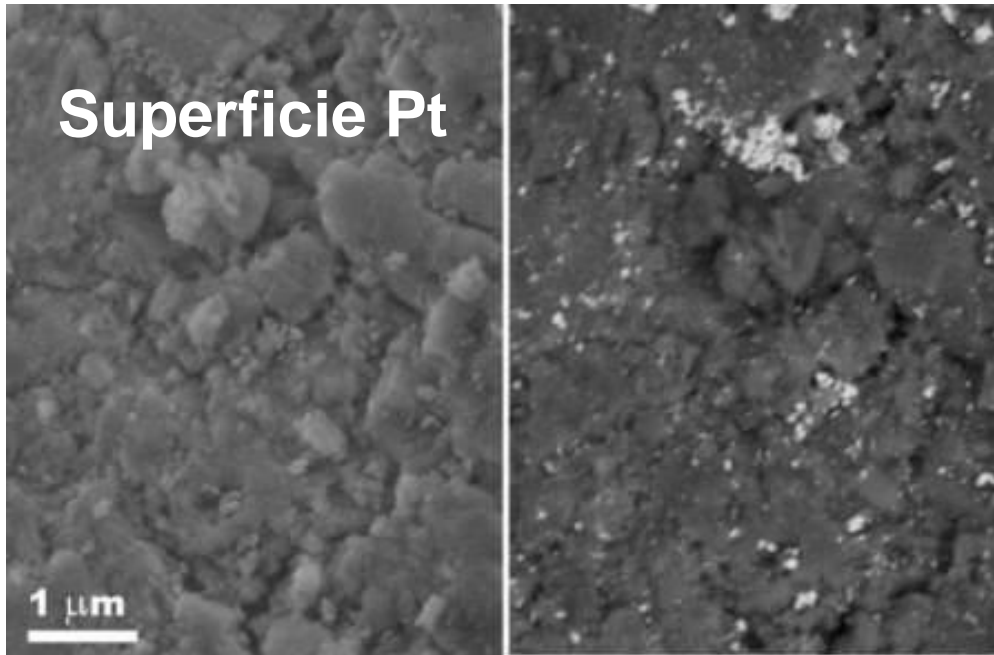
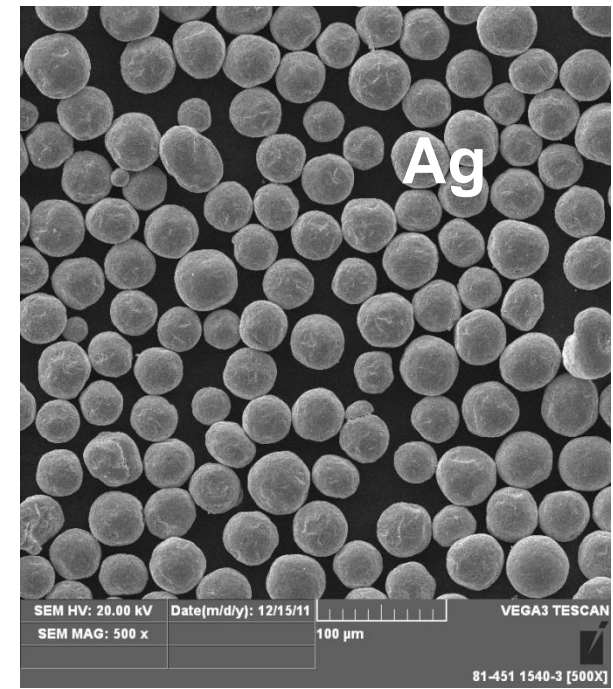
ANALIZO borde de absorción de un elemento dado

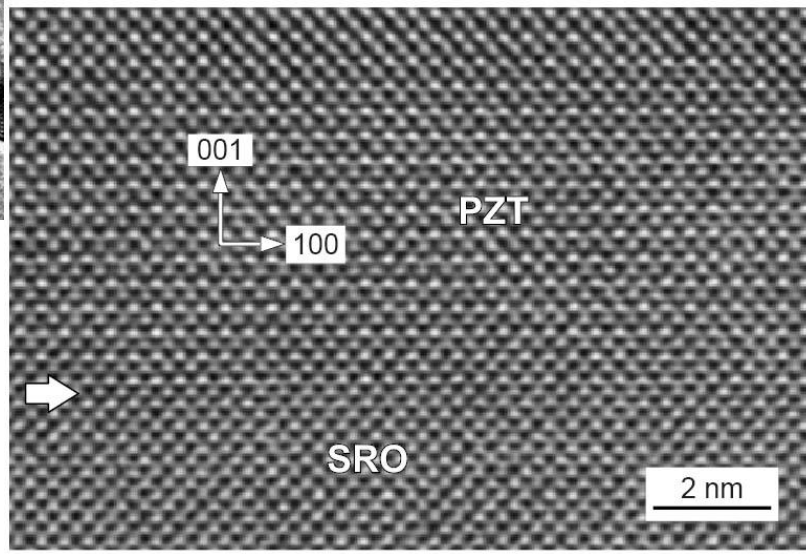
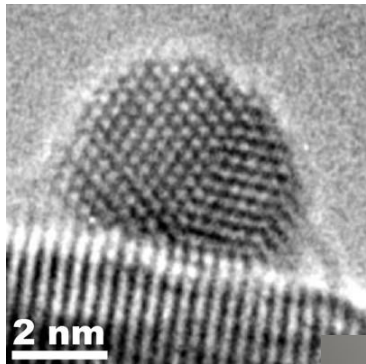
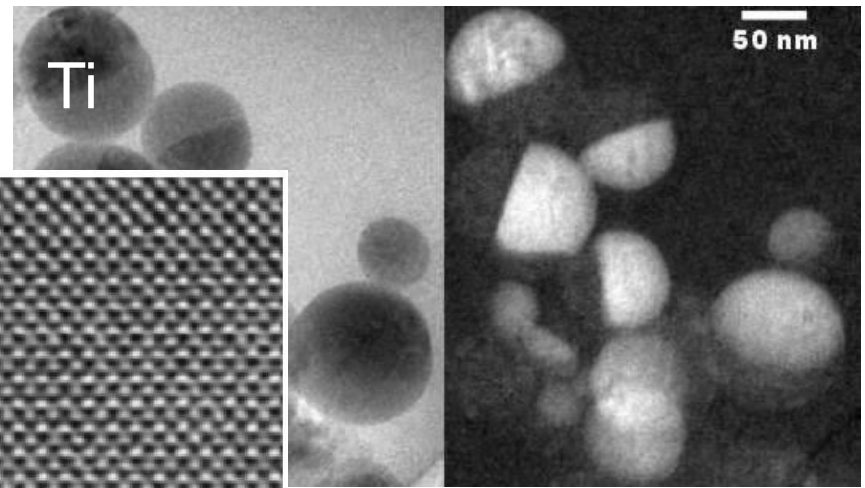
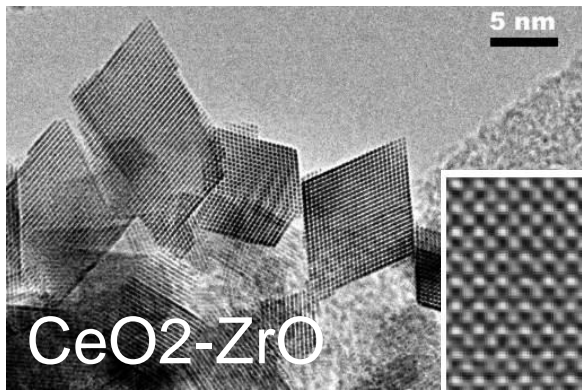


MICROSCOPIAS

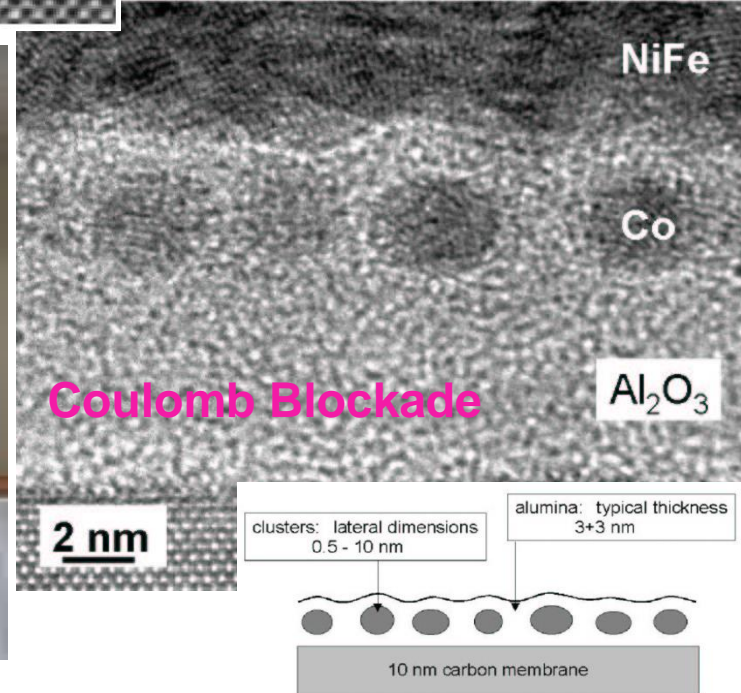
- SEM
- TEM
- Sonda local (AFM, STM, MFM, PFM....)

SEM

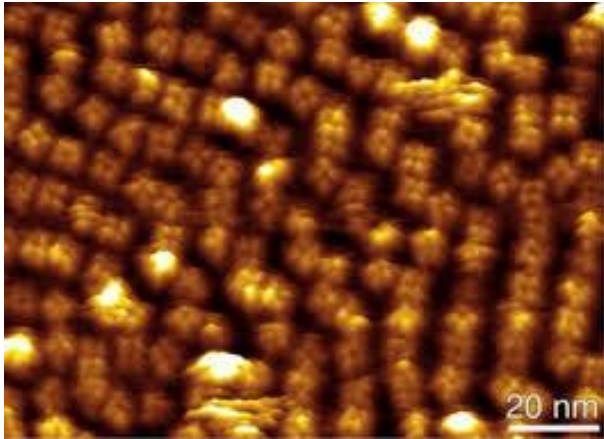
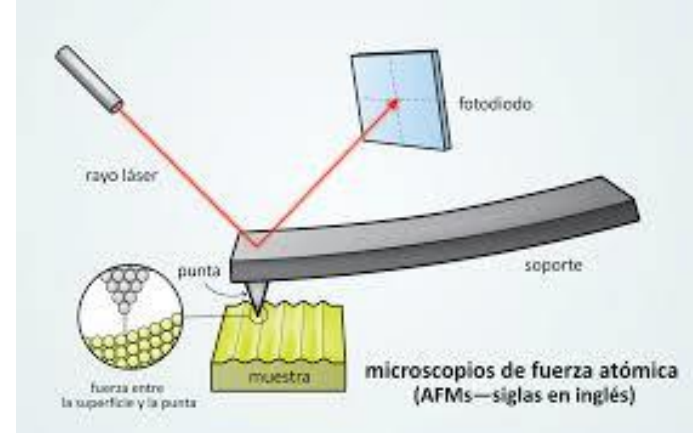




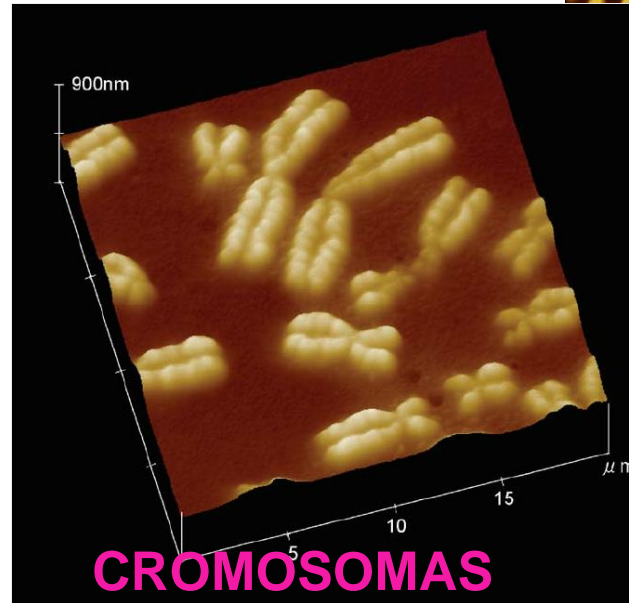
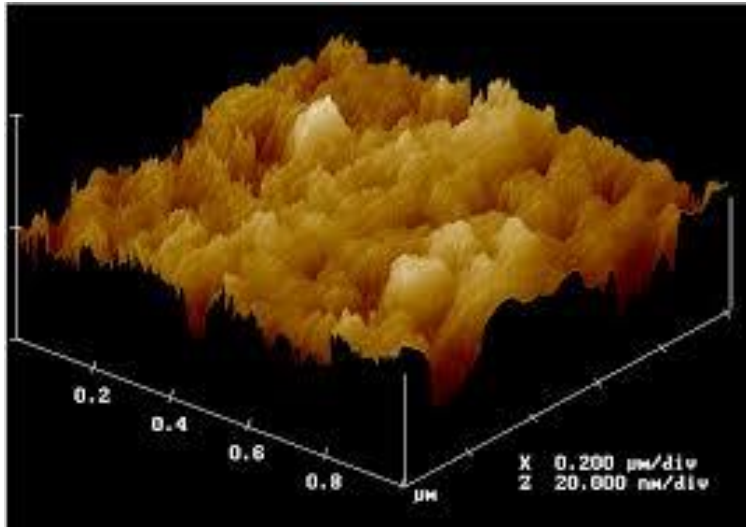
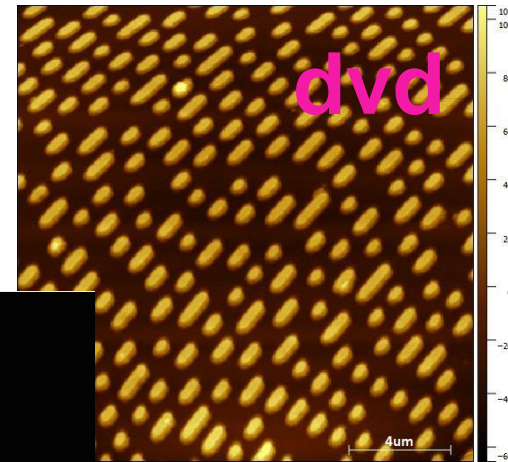
HR-
TEM



MICROSCOPIAS DE SONDA LOCAL

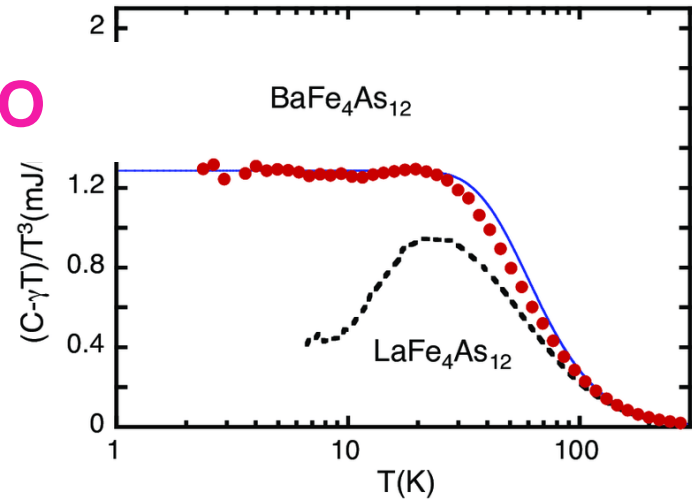
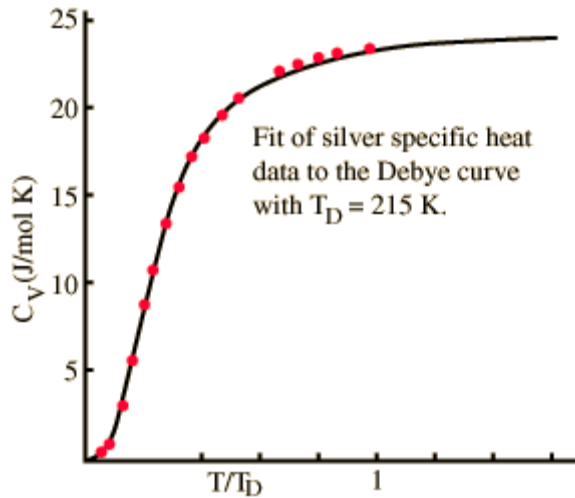


AFM



FONONES

CALOR ESPECIFICO



RELACION de DISPERSION FONONES

NEUTRONES Inelastic X-RAY SCATTERING

Optica

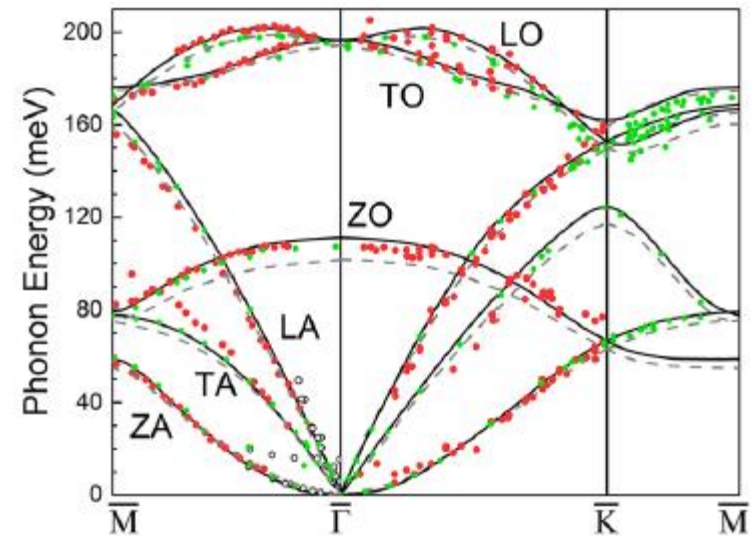
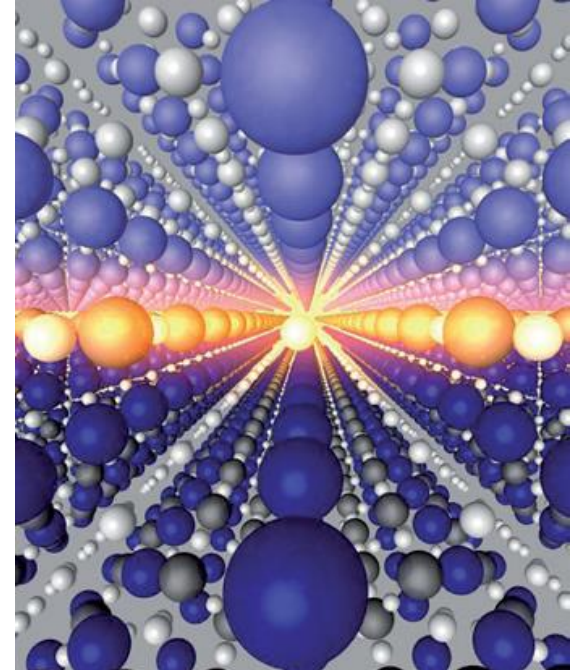


Figure 2. Phonon dispersion of graphite from HREELS (red dots, [54, 55]), inelastic x-ray scattering (green dots, [53]) and inelastic neutron scattering (open circles, [56]). DFT calculations for Gr are shown by gray-dashed lines [57] and solid lines [58].

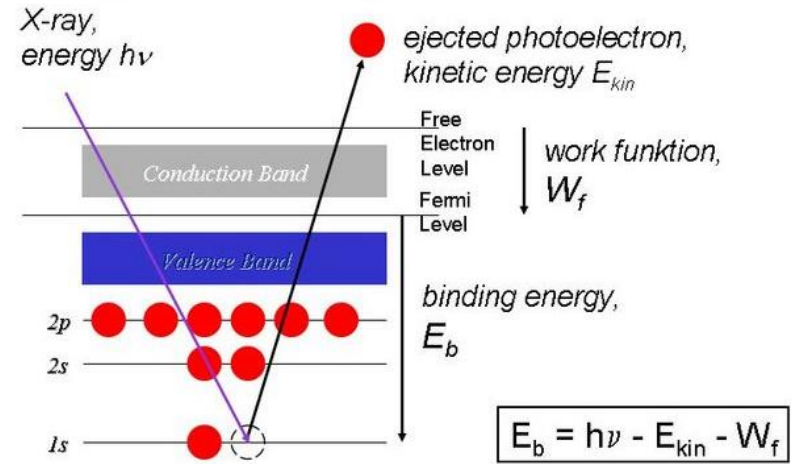
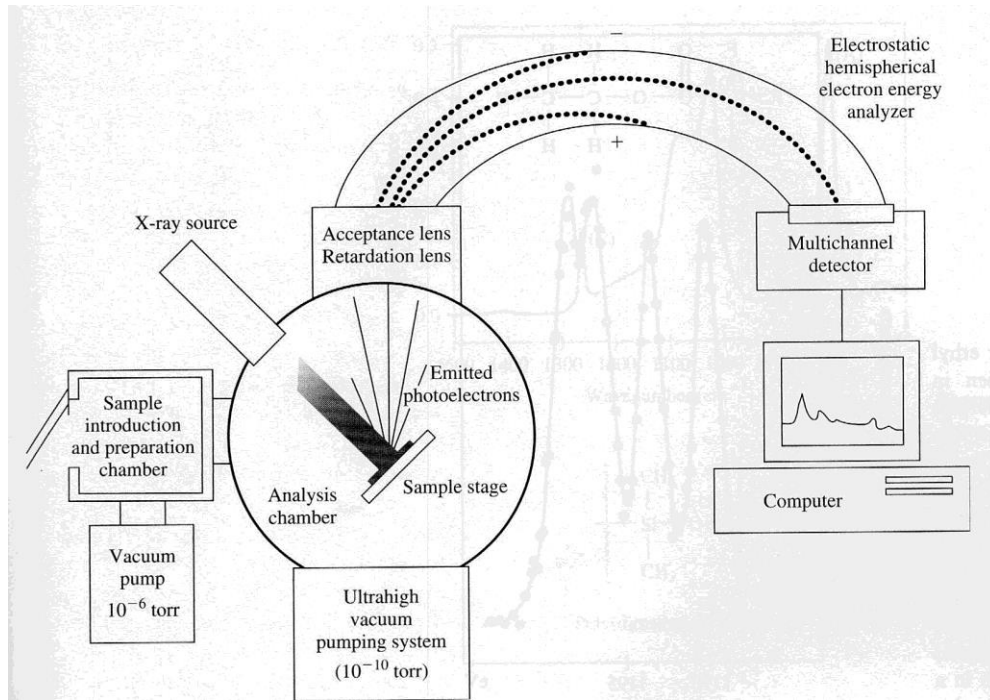
ELECTRONES

Técnicas de caracterización en superficies -

- Excitación: rayos X, UV, electrones, iones
- Detección: rayos X, electrones, iones....
- Longitud de penetración: algunos nm, dependiendo de la técnica



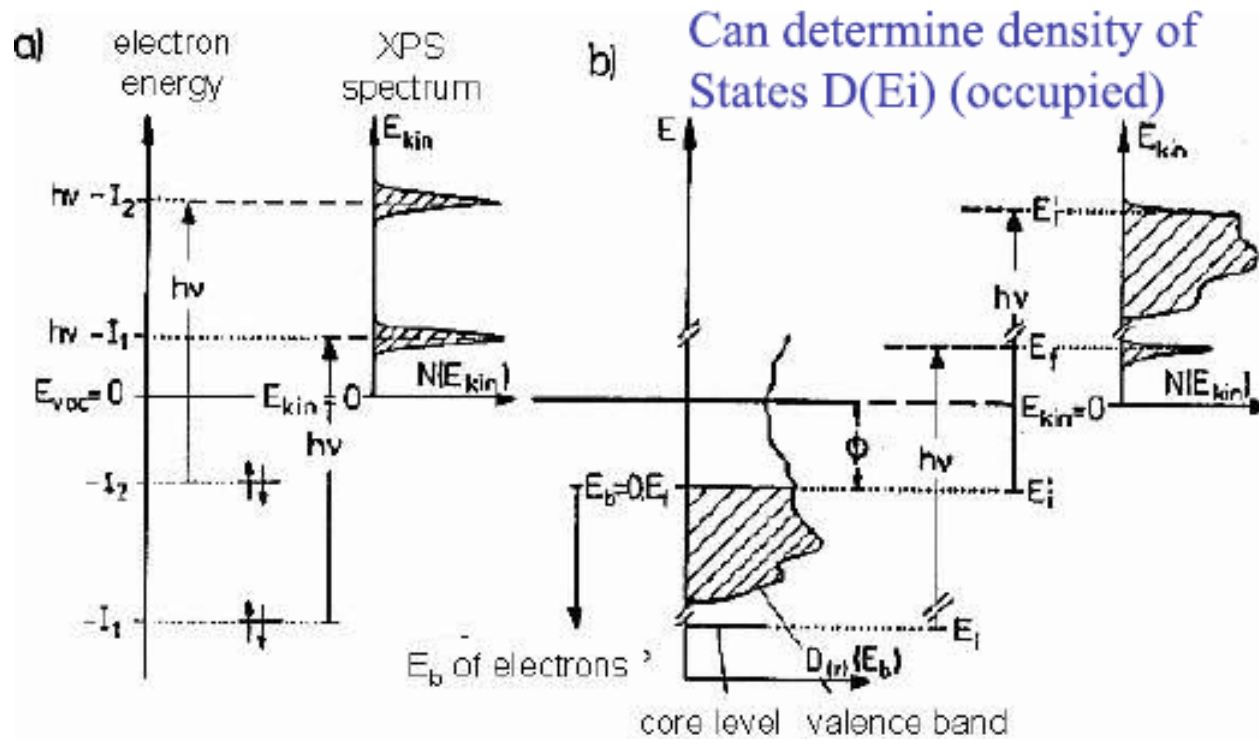
X-ray Photoelectron Spectroscopy XPS



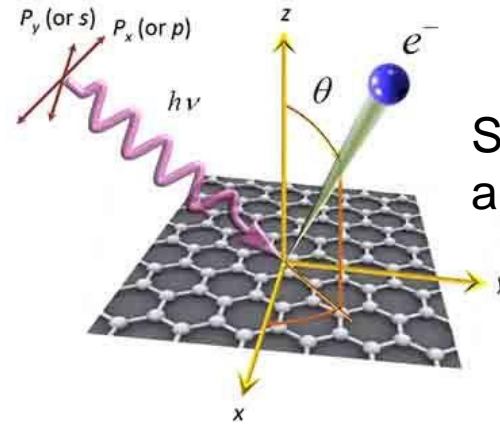
Electrons emitidos como resultado de la incidencia de los rayos X son separados de acuerdo a su energia cinetica y contados en un detector

Ultraviolet Photoelectron Spectroscopy (UPS)

UV light ($h\nu = 5$ to 100 eV) to excite photoelectron. From an analysis of the kinetic energy and angular distribution of the photoelectrons, information on the **electronic structure** (band structure) of the material under investigation can be extracted with surface sensitivity.

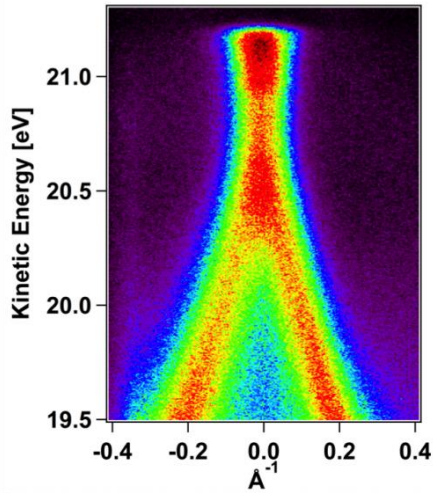


Angle Resolved Photoemission Spectroscopy ARPES

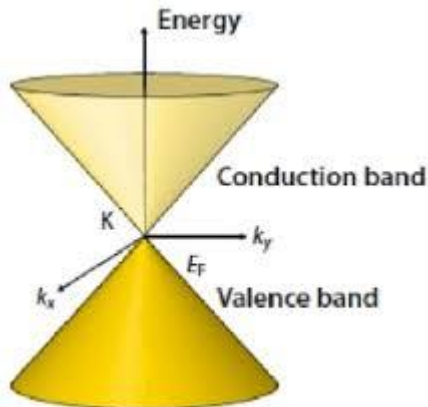
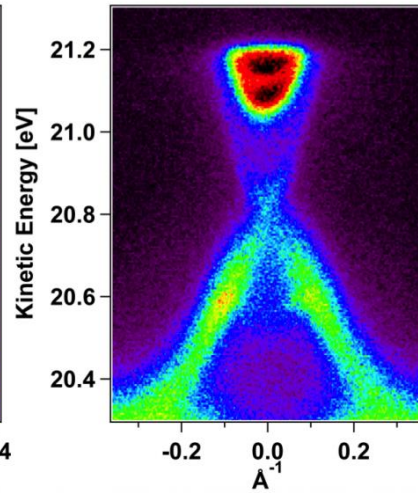


Se mide Eel + angulo θ

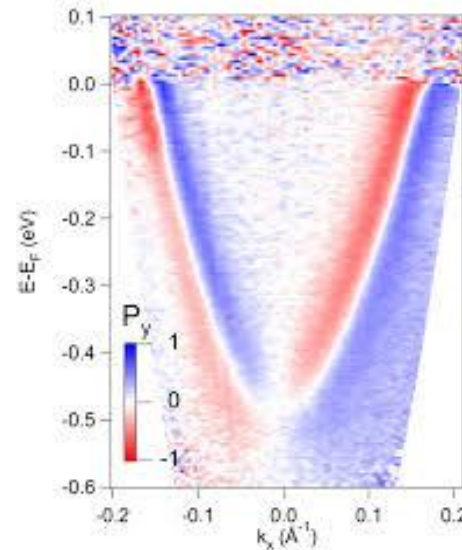
Epitaxial Graphene on SiC
NRL - Kurt Gaskell



Bi₂Se₃ on Sapphire
UTD - Chris Hinkle



Conos de Dirac



Spin-resolved ARPES

SCANNING TUNNELING MICROSCOPE

Microscopio STM-AFM de ultra alto vacío y variable en temperatura (25 – 1000K) // CAB

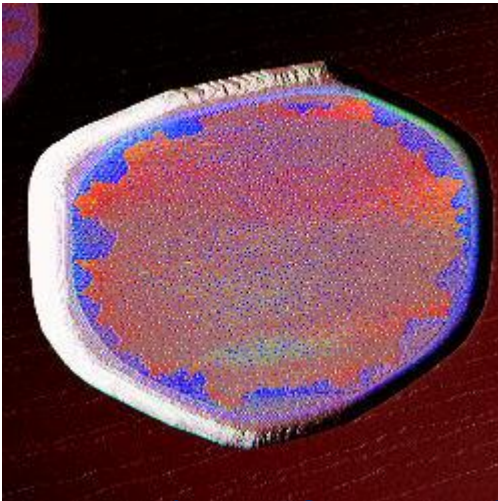
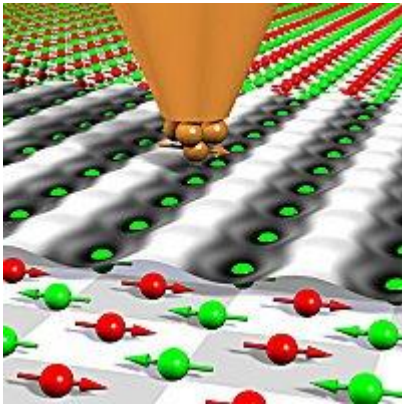


Image size: 450 nm x 450 nm



STM images

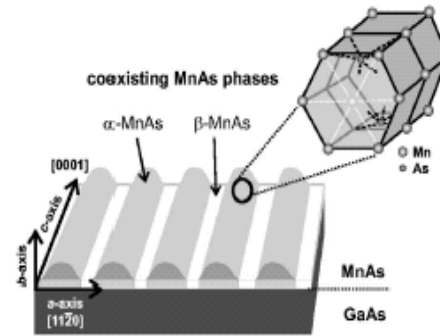
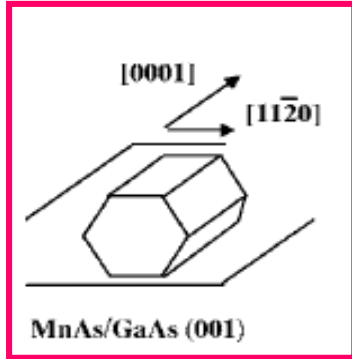
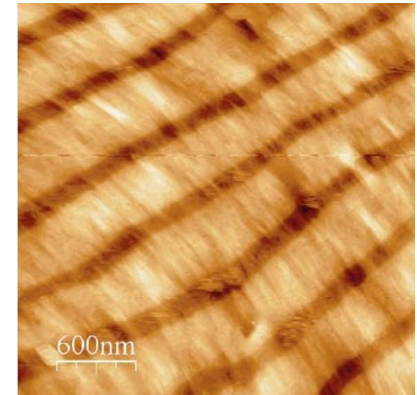
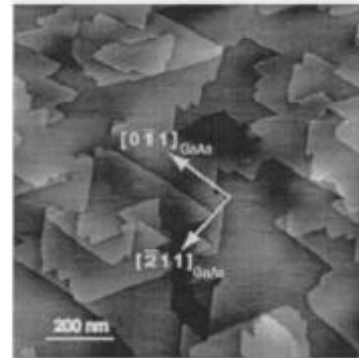
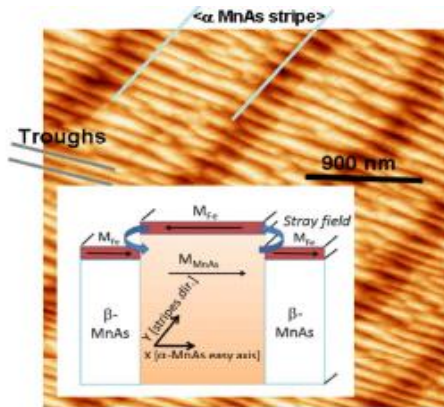


FIG. 1. Sketch of the stripe structure of the strain-stabilized coexisting α - and β -MnAs phases on GaAs(001) in the temperature range from 10 to 40 °C. The in-plane a axis is the easy axis of magnetization and the magnetic hard axis is along the in-plane c -axis direction (MnAs[0001]). On the top right, a detailed sketch of the hexagonal α -MnAs cell is shown.

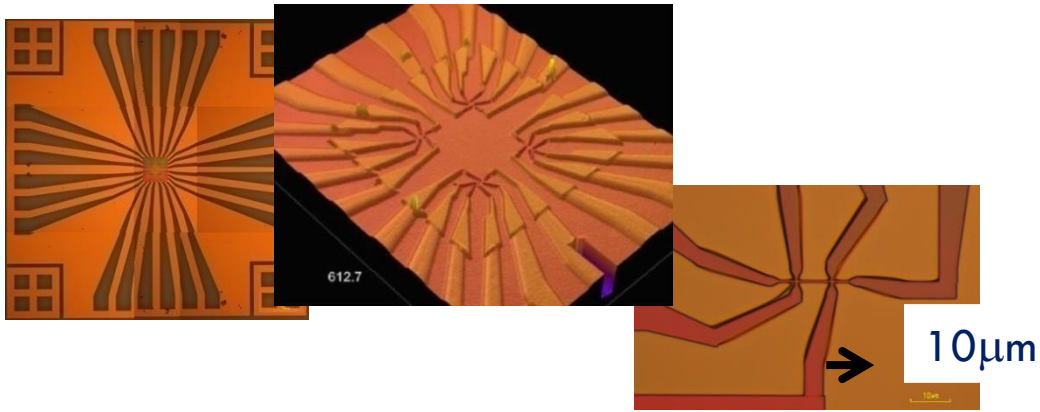


TRANSPORTE ELECTRONICO

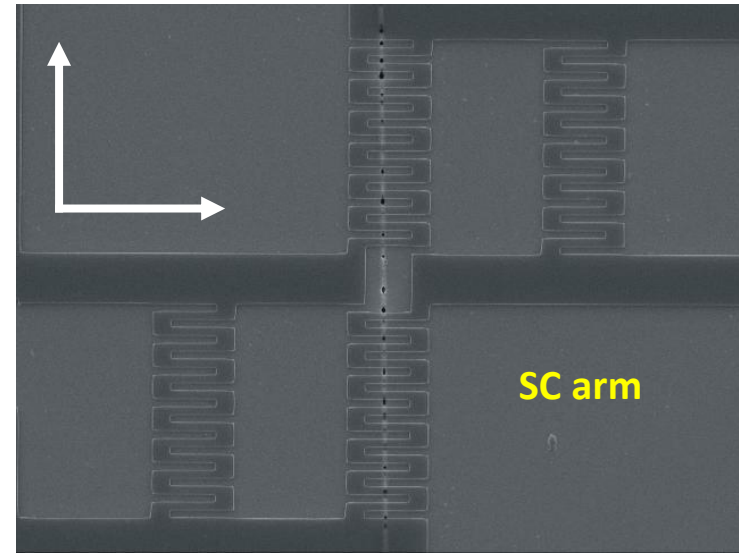
- Resistividad \rightarrow difusivo (semi-clasico), $R(T)$ se pueden analizar mecanismos de scattering
- Hall effect $R_{xy}(H)$: numero y tipo de portadores
- Haas van Alphen $R(H)$ podemos sondear superficie de Fermi
- Balistico Fermi, interferencia (onda):
cuantica

Medidas de efecto Hall y magnetoresistencia

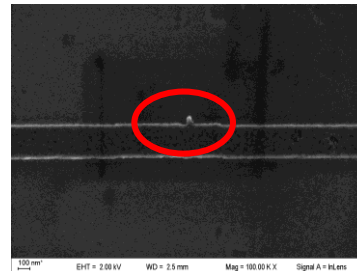
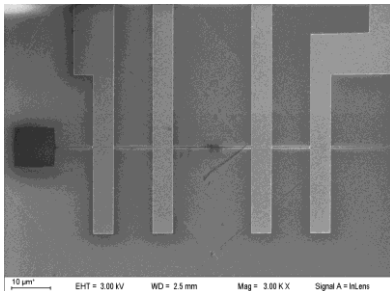
Grabado micro y nanohilos con contactos eléctricos sobre films de MnAs por litografía



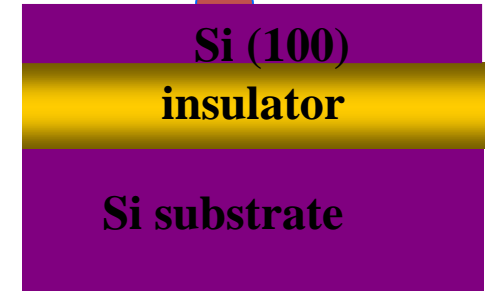
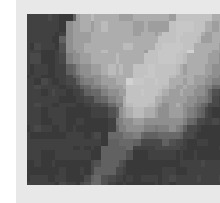
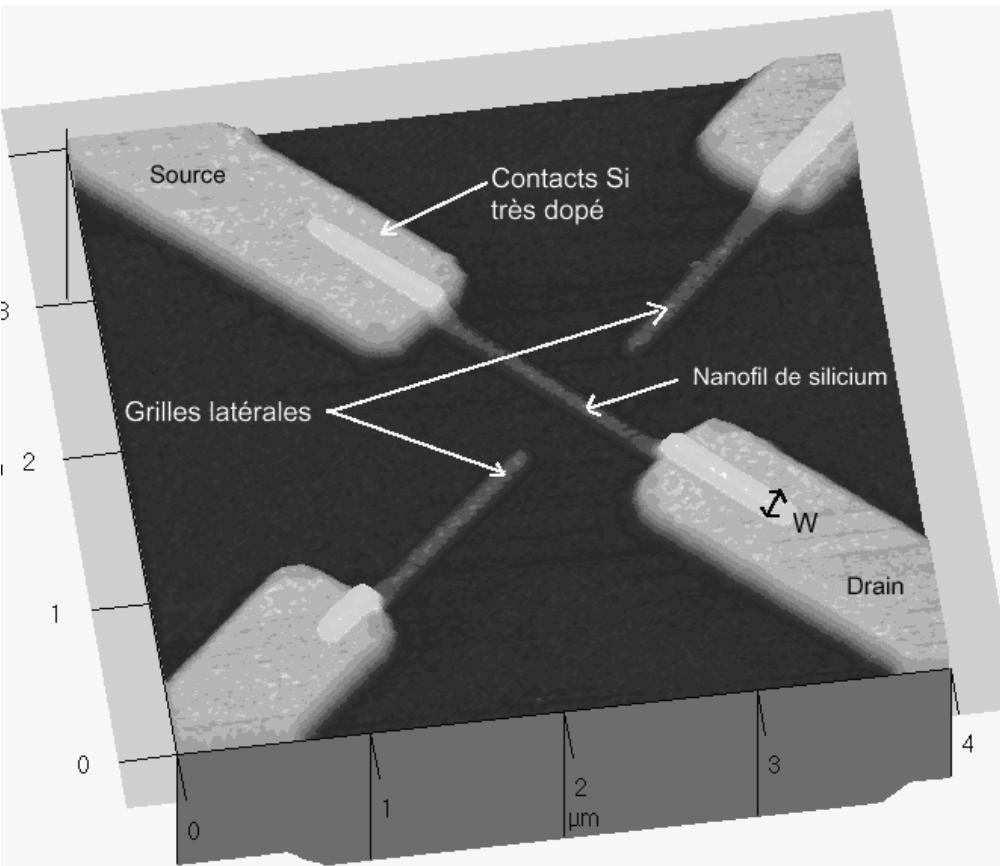
GB arm



MR en nanohilos de oxidos!
Defectos de distintas geometrias y
tamaños

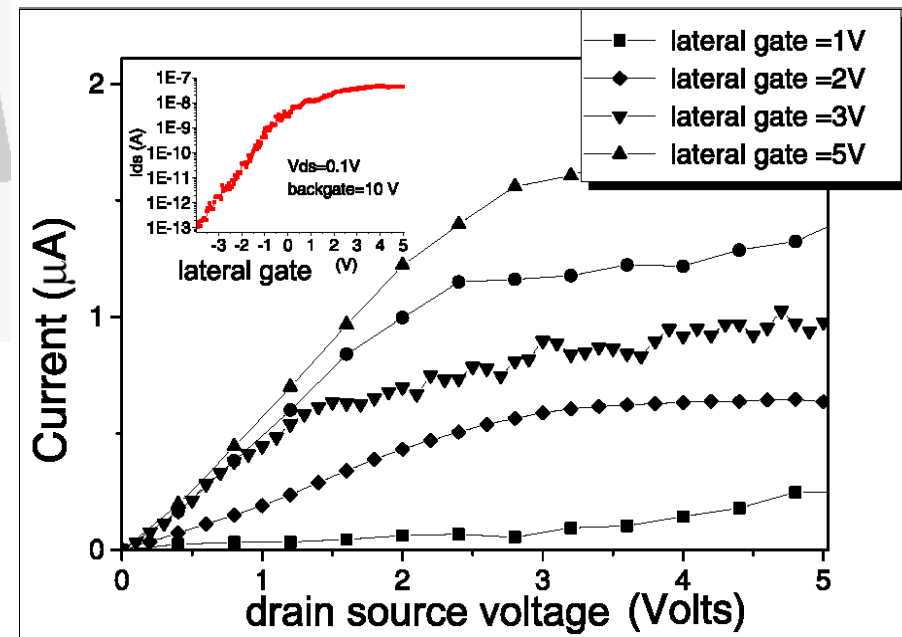


Connecting structures: nano-transistor

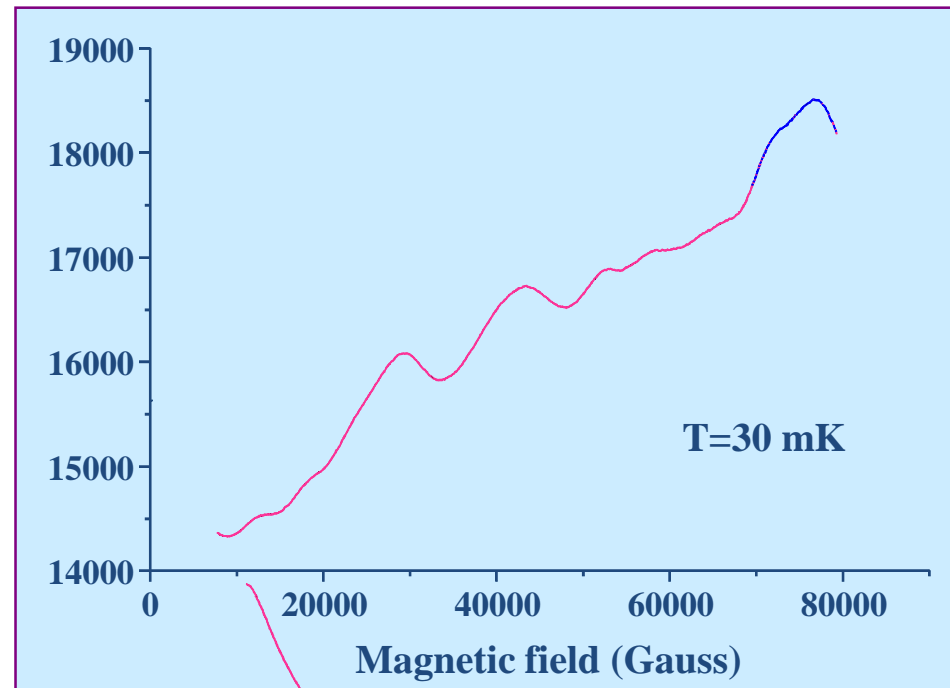
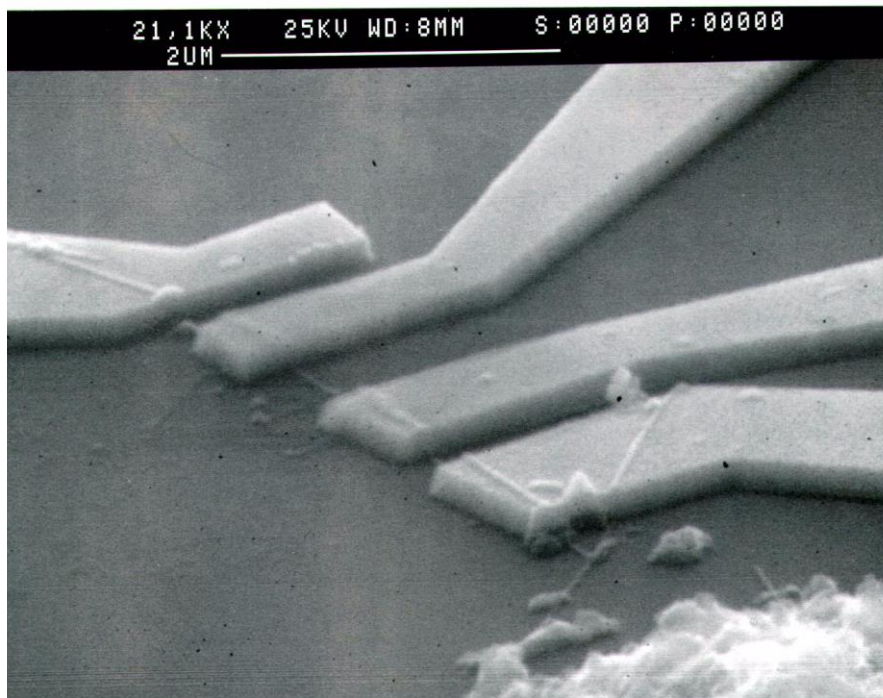


Electric test pattern on SOI substrate provided by the CEA-LETI laboratory (France-Grenoble)

IN Grenoble

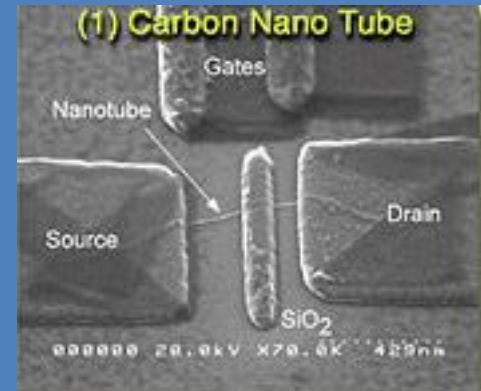
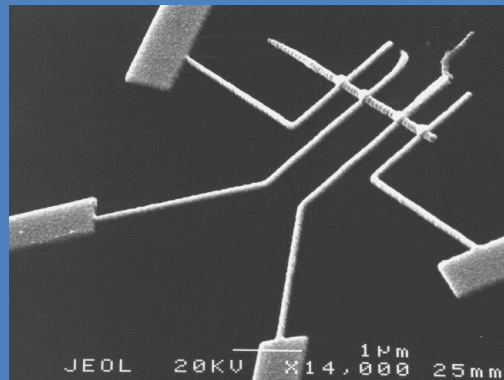
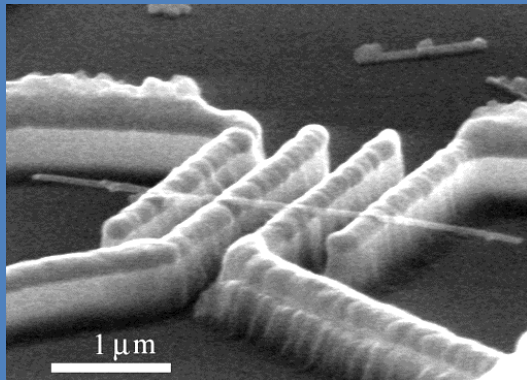
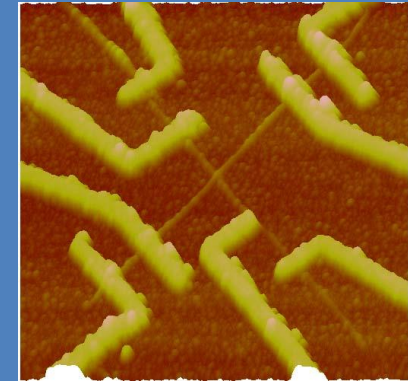
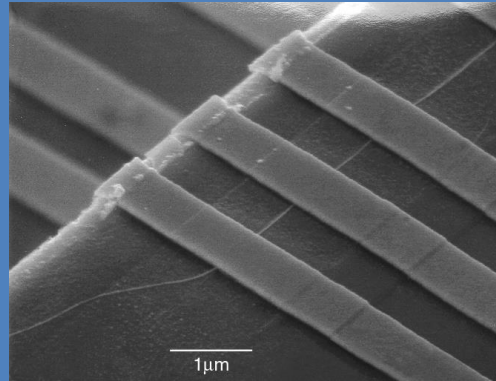
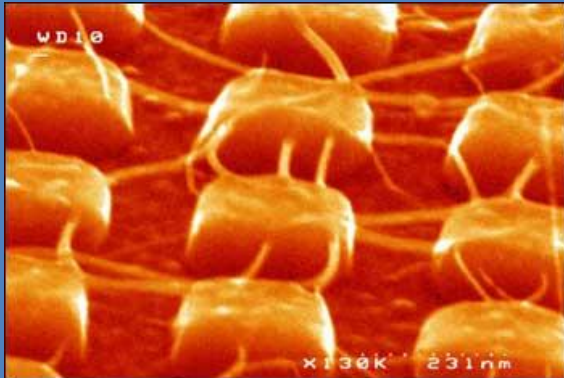


Nanotubos de carbono y EBL



C.Naud, G.Faini, D.Mailly, H.Pascard, C.R. Acad. Sci. Paris 327, Série IIb (1999)

Distintas aproximaciones

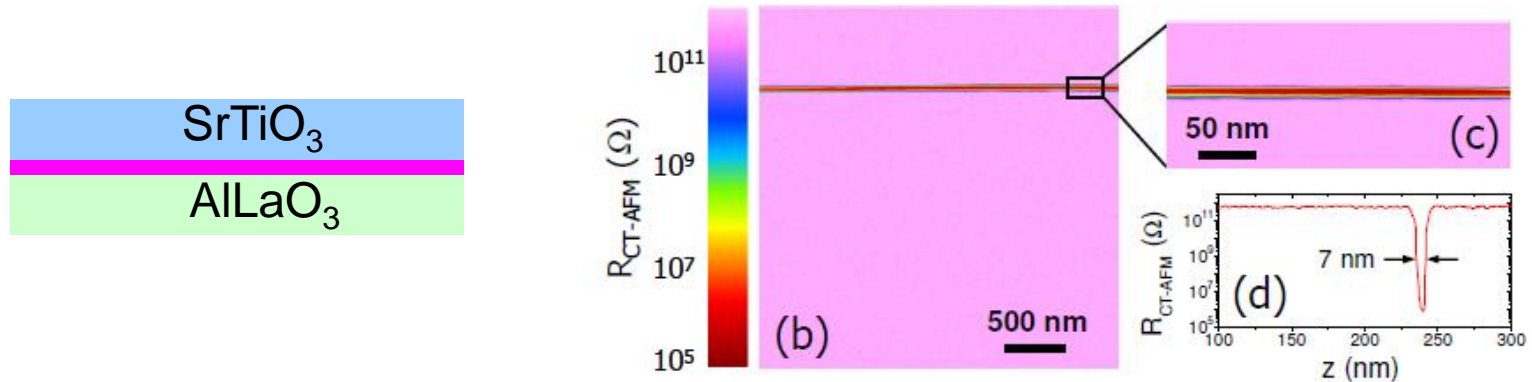


Different kind of systems:

Carbon nanotubes; semiconductor, magnetic, superconductor nanowires

Efectos de interfaces: aparecen fenomenos inesperados...

Deteccion de un gas de electrones 2D entre dos aislantes SPM



MAGNETISMO

- **TRADICIONALES**
- **Magnetometria**
- **MOKE**
- **FMR**

- **SUPERFICIES**

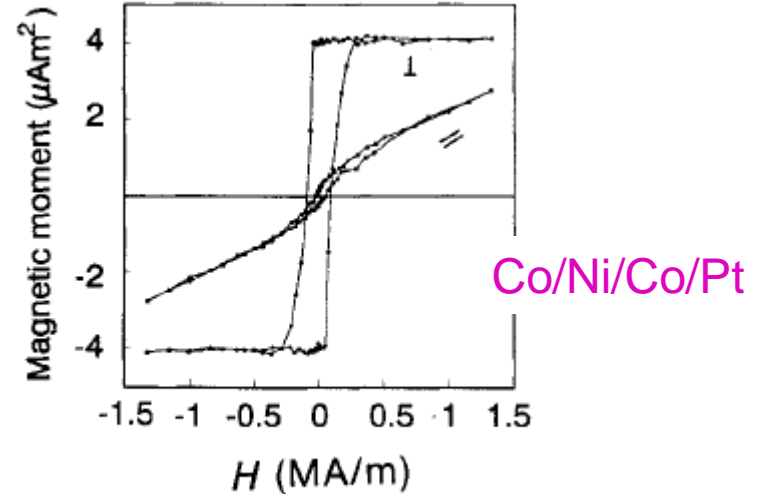
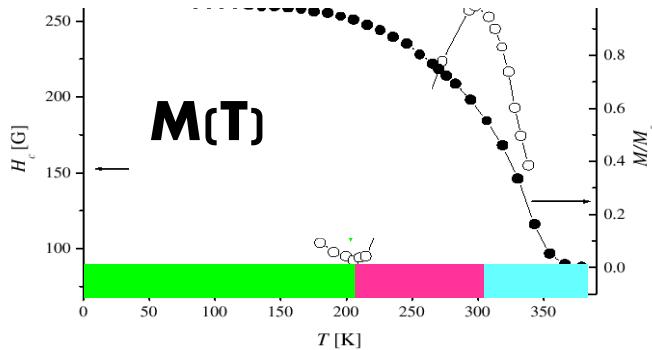
Fuentes de electrones polarizados o analizadores

- **SONDA LOCAL**
STM, MFM

MAGNETOMETRIA

Ciclo de histeresis $M(H)$

MnAs 100nm/GaAs(111)



- * Equipos de distinta sensibilidad: **SQUID** 10^{-8} emu
VSM 10^{-6} emu
- * **TODOS SENSAN VOLUMEN**
- * **Trabajan a distintos campos magneticos y temperaturas**

Estudio de orden magnetico, anisotropias, acoplamientos entre capas

FMR espectrometro de resonancia magnetica electronica

MEDIDA DE VOLUMEN

TECNICA MUY SENSIBLE: PARTES POR MILLON
MEDIDAS DE ANISOTROPIA MAGNETICA,
EXCITACIONES, ACOPLAMIENTO INTERCAPAS

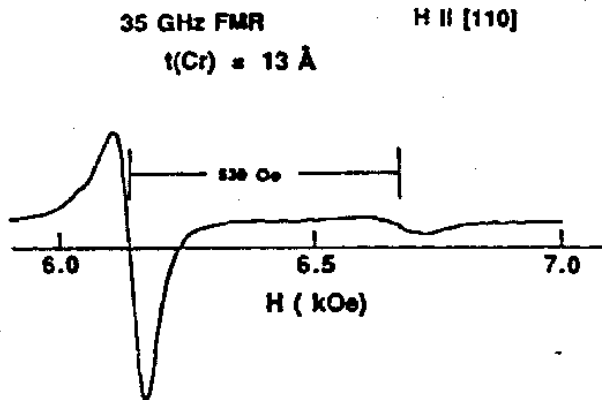
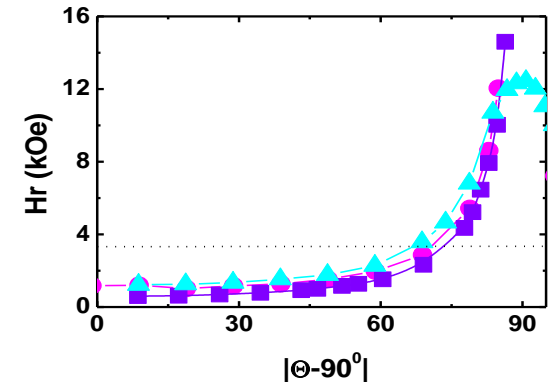
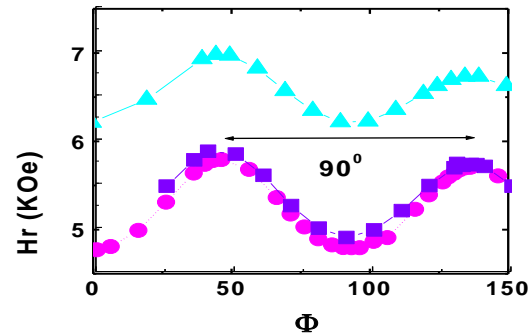


FIG. 6. Derivative FMR spectra of an Fe/Cr/Fe(001) sample at 35 GHz showing the out-of-phase antiferromagnetically coupled mode which occurs at a field $4J$ above the regular in-phase mode.

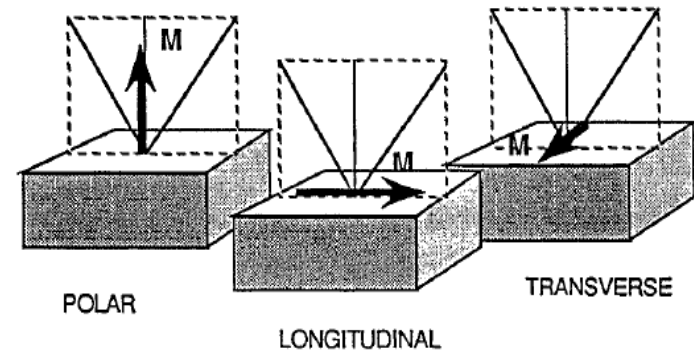
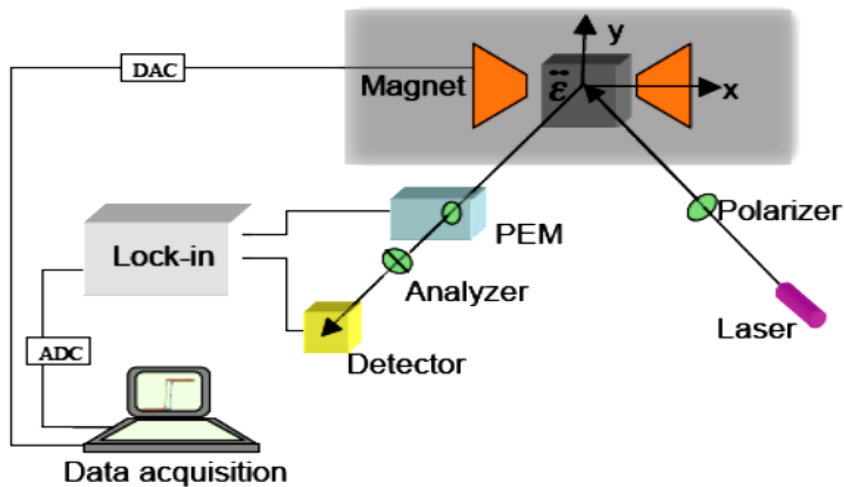


Magneto-Optical Kerr Effect (MOKE)

Interaccion de luz con la magnetizacion del material: cambio de polarizacion del haz incidente

Resolucion lateral: diametro haz : decenas de μm

Distintas geometrias



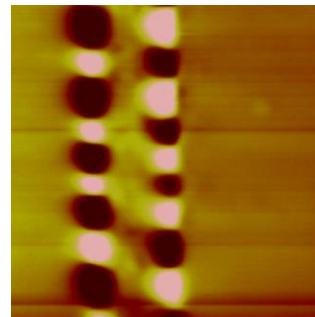
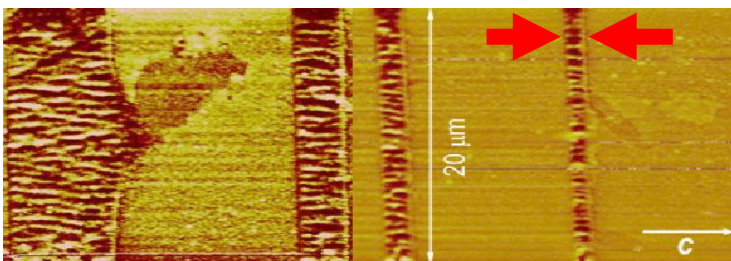
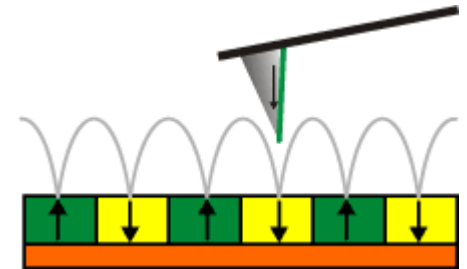
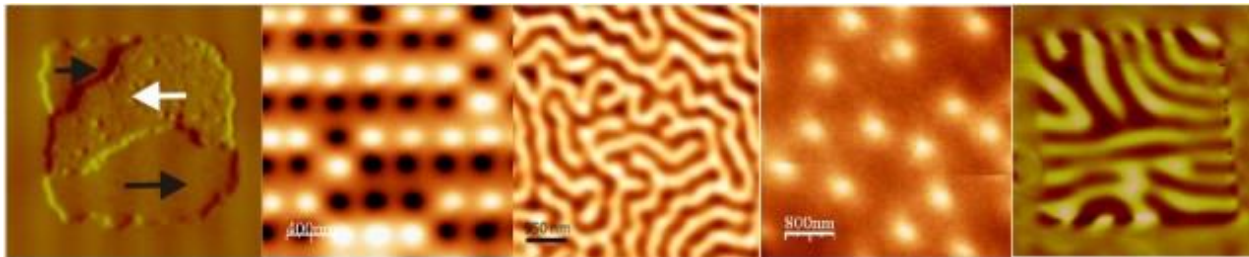
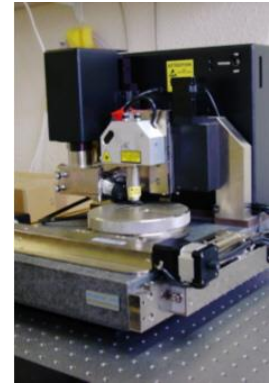
M contenida en el plano de incidencia y reflexion de luz (polar y longitudinal) o perpendicular (transversal)

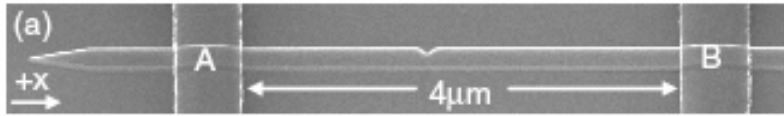
RESOLUCION LATERAL: SUBMICROMETRICA

MICROSCOPIA DE FUERZA MAGNETICA

Detecta fuerza de Van der Waals y dipolar

La estrategia es medir a distintas distancias de la muestra para poder diferenciar topografía de señal magnetica



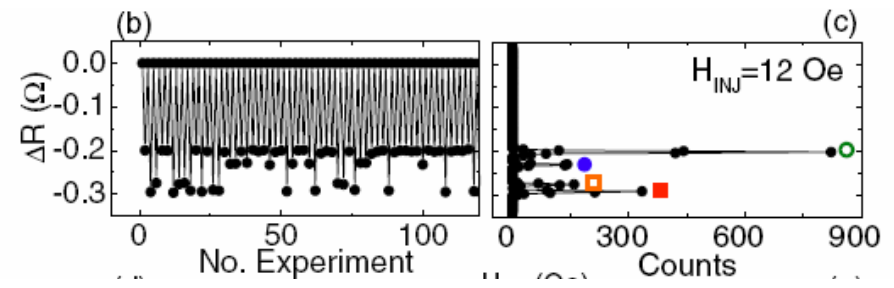
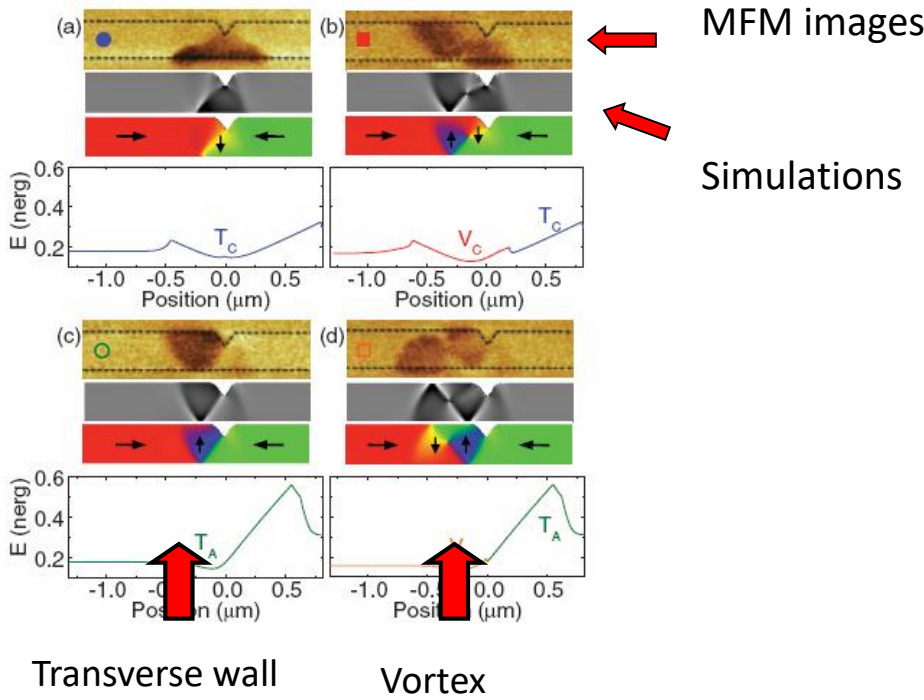


M. Hayashi *et al*,
 Phys. Rev. Lett. **97**, 207205 (2006)

$\text{Ni}_{81}\text{Fe}_{19}$
 WIDTH: 300 nm, THICKNESS: 10nm

Domain walls are created and moved by I injection

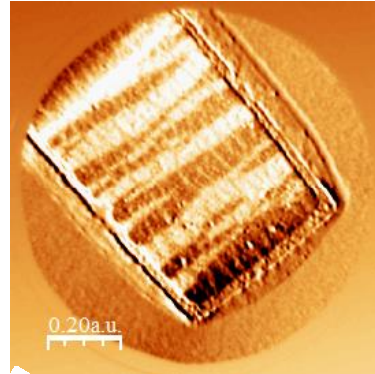
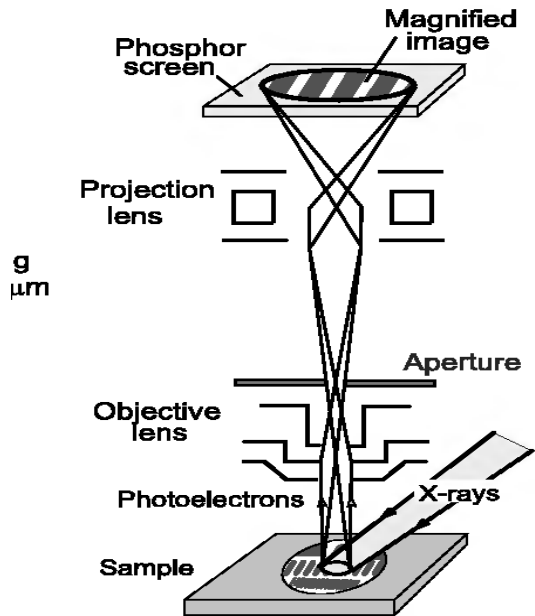
Charge – spin interaction



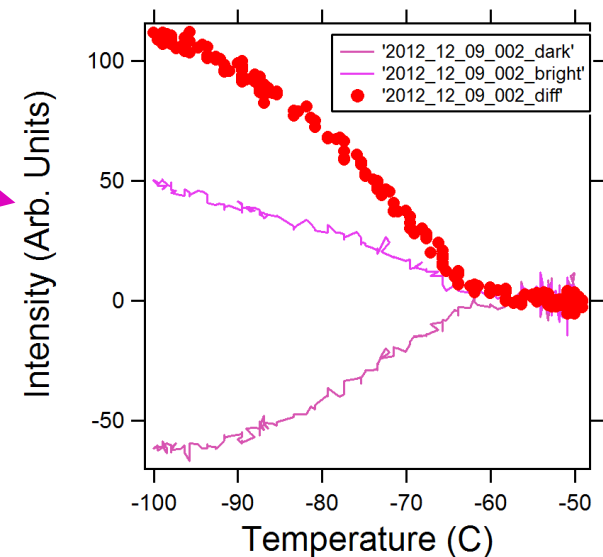
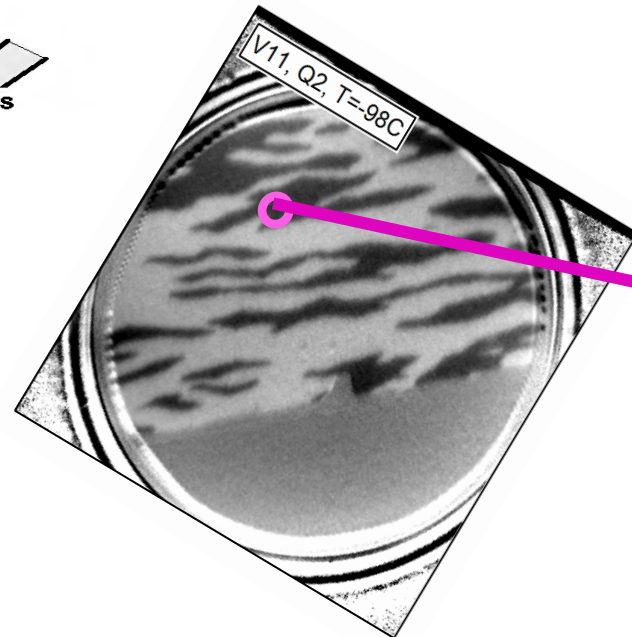
XPEEM

Photoemission Electron Microscopy tiene una resolución espacial de entre 50- 100nm para resolver estructuras relevantes

Photo Emission Electron Microscopy PEEM



**Mapeo magnetización
mediante el análisis
de electrones secundarios
* especificidad elemental!**



TECNICAS DE ANALISIS DE SUPERFICIE POLARIZADA EN ESPIN

PERMITEN MEDIR FILMS ULTRA FINOS \Rightarrow NM
RESOLUCION LATERAL: TAMAÑO HAZ O RESOLUCIÓN ANALIZADOR

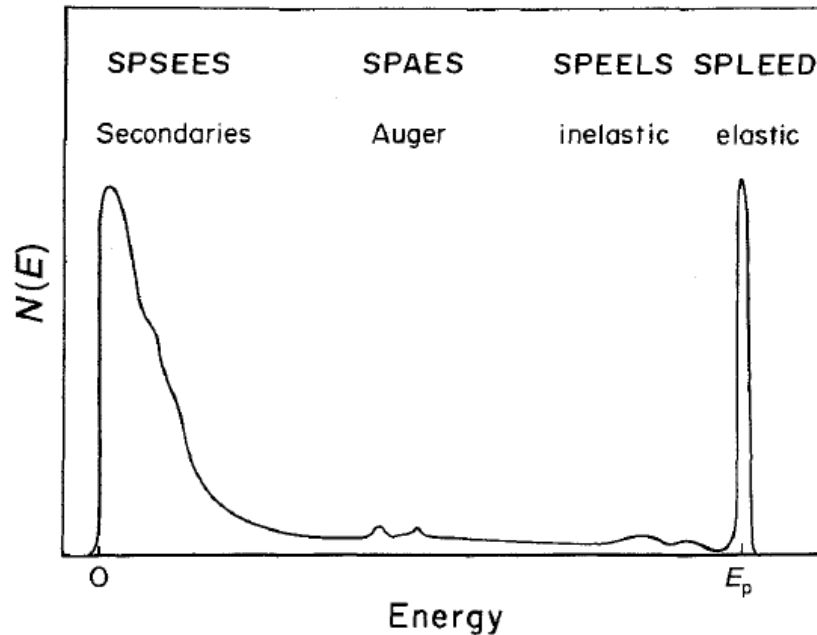


Fig. 4.1. Schematic electron energy spectrum

Espectroscopias de Superficies de electrones polarizados en espin

Fuentes polarizadas en espin o detectores de polarizacion!

MEDIDAS DE MAGNETOMETRIA CON TECNICAS DE ELECTRONES POLARIZADOS

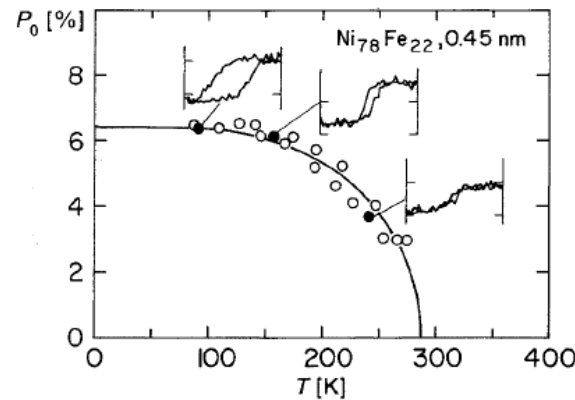
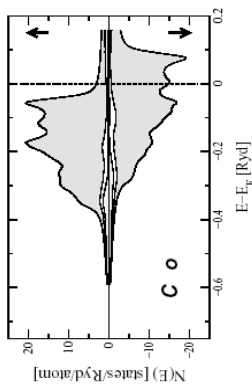


Fig. 4.22. Spin polarization $P_0(T)$ obtained by extrapolation of $P(H,T)$ to $H \rightarrow 0$ for a 0.45 nm

Medida de magnetizacion de una monocapa de aleacion

marks on the ordinate indicates a 10% change of spin polarization and the applied field is swept from -2.0 to $+2.0$ kA/m. Data from [4.177, 165]

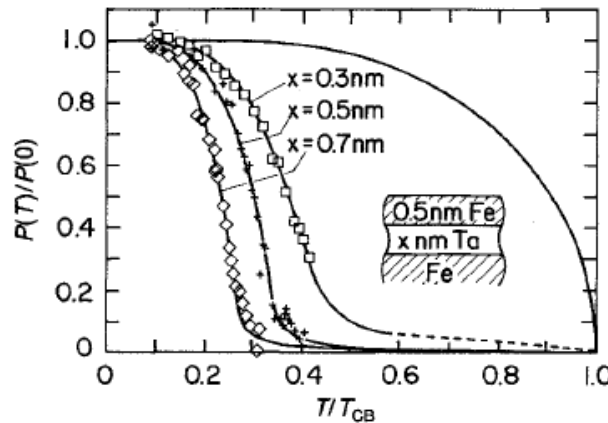
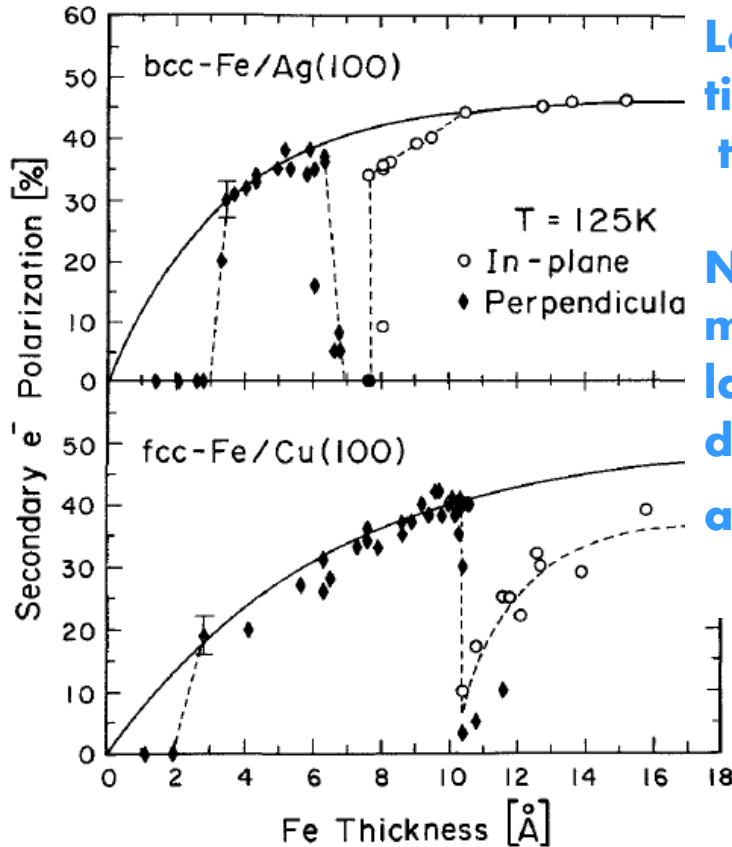


Fig. 4.25. Relative spin polarization $P(T)/P(0)$ of the low energy cascade extracted from the 0.5 nm monolayer

Medida de magnetizacion de una monocapa de Fe separada de un macizo de Fe Observar cambio 2D respect a 3D

variations. The mean field curve for bulk Fe ($H_{ex} = 0$) is shown to illustrate the crossover from 2D to 3D magnetism

Medida de la polarización de electrones secundarios en films de Fe de distintos espesores => magnetización!



La zona donde la M del film pasa de OOP a IP tiene un ancho finito donde cae la polarización total

No se sabe si hay una perdida de magnetizacion real en esa zona o si la medida indica un split de la M en dominios (las medidas fueron hechas a $H=0$)

XPS polarizado en espin

Se puede sintonizar bandas de distinto spin

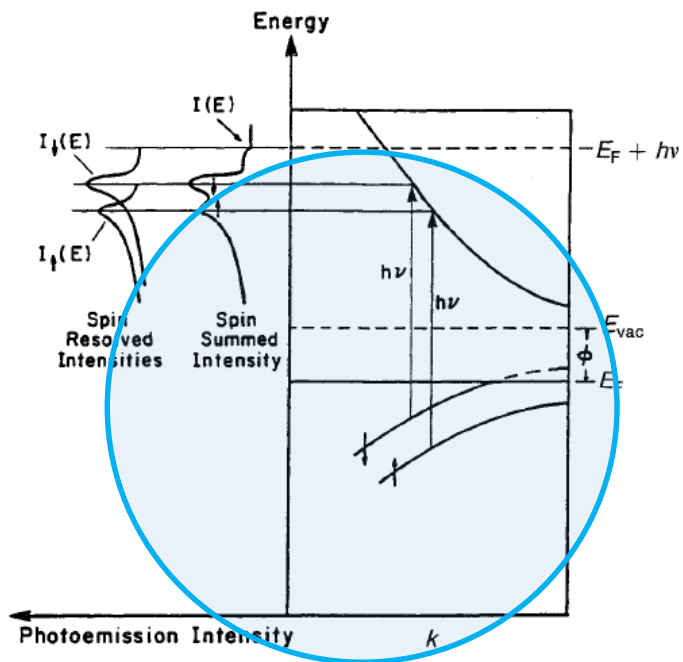
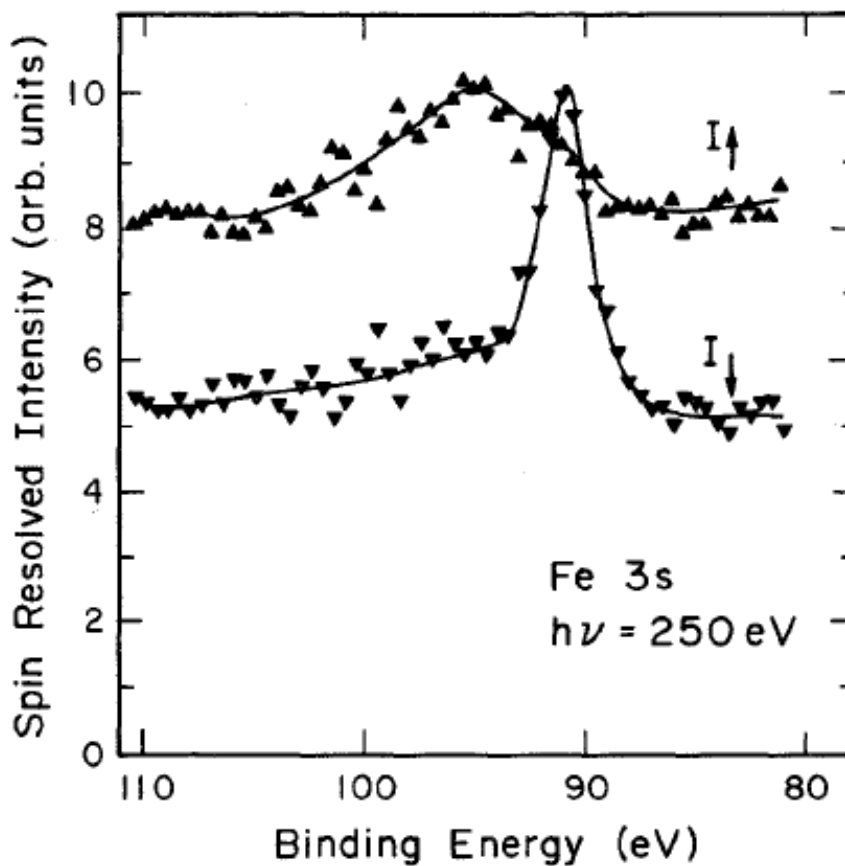


Fig. 4.16. Schematic of the photoemission process

Detalle espectro líneas de niveles del Fe (3s)
Intensidad dependiente de espin (XPS)



GRANDES FACILIDADES: CAMPOS MAGNETICOS INTENSOS

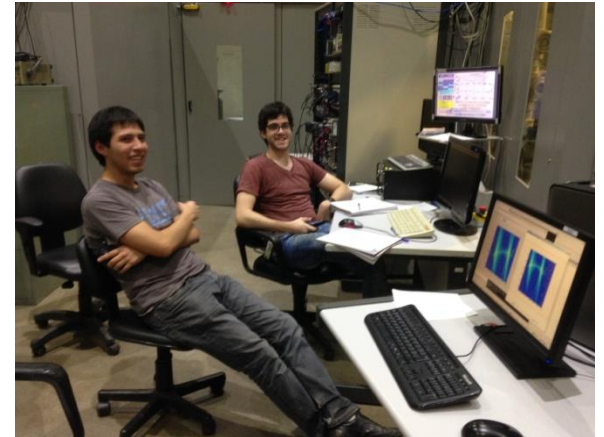
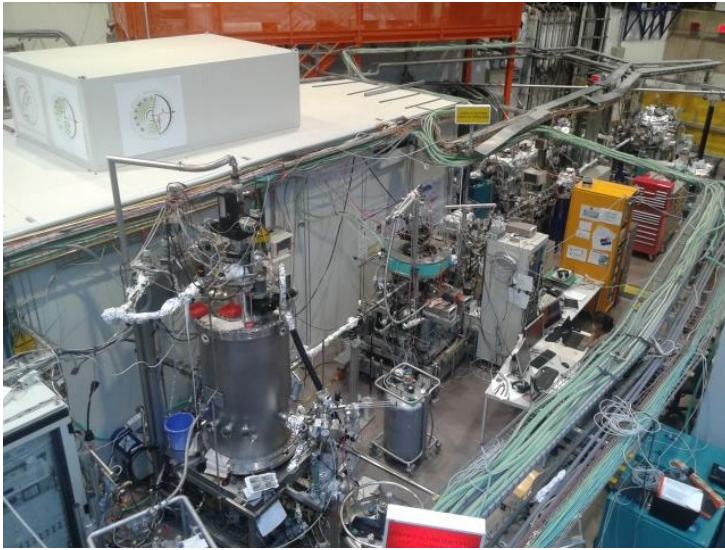


LOS ALAMOS NHMFL USA

HASTA 100T
MAGNETISMO, ELECTRONICA

SINO CAMPOS PULSADOS HASTA
CAMPOS MAS ALTOS

FACILIDADES DE RADIACION SYNCHROTRON



100 o mas mts de diametro